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ALL-DIGITAL RF SIGNAL GENERATION USING $\Delta\Sigma$ MODULATION FOR MOBILE COMMUNICATION TERMINALS

GENERATION NUMERIQUE DE SIGNAUX RF POUR LES TERMINAUX DE COMMUNICATION MOBILE PAR MODULATION $\Delta\Sigma$

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Abstract

All-digital RF signal generation using $\Delta\Sigma$ modulation for mobile communication terminals

Mobile communication applications increasingly demand ubiquitous access to wireless networks across multiple standards and frequency bands. Software radio architectures implemented in advanced nanometer scale technologies are largely investigated to meet this challenge. In particular, the interface from the digital to the analog/RF world is projected to move as close as possible towards the antenna. In this work a digital transmitter architecture based on $\Delta\Sigma$ modulation is investigated, and a prototype digital RF signal generator has been implemented to prove the feasibility of the concept.

The proposed architecture is built around two oversampled 3^{rd} -order lowpass digital $\Delta\Sigma$ modulators that provide a multiplexed high-speed 1-bit data stream directly coding the RF signal in the digital domain. The modulators noise-shaping transfer functions move the quantization noise out of the transmit band of the considered standard, allowing to reach a high signal-to-noise ratio and extremely low distortion in the transmit band. The output stream can then be fed to an efficient switching-mode power amplifier.

The UMTS standard has been taken as the application example, and a digital RF signal generator providing the 1-bit output stream at 7.8Gs/s has been designed in a 90nm CMOS technology. The effective sampling rate of the low-pass $\Delta\Sigma$ modulators is in this case 3.9GS/s. Thorough optimization at the architectural and logic level was mandatory: quantized modulator coefficients, redundant arithmetic with complementary signal paths, non-exact output quantization and anticipated output evaluation have been implemented to reach the high sampling rate. 3-phase differential dynamic logic clocked by a DLL has been used at the circuit level.

The fabricated prototype transmitter IC demonstrates full functionality up to a 4GHz main clock frequency, reaching a maximum bandwidth of 50MHz at 1GHz center frequency with a 3.1dBm peak output power. When using the first image band, the transmit band can be moved up to 3 GHz, however with reduced output power due to the sin_c shaping function.

With a 2.6GHz main clock frequency and 5MHz WCDMA modulated channel at a carrier frequency of 650MHz, a channel output power of -3.9dBm and 53.6dB of ACPR are obtained. With the same settings, a channel output power of -15.8dBm and an ACPR of 44.3dB is reached in the 1.95GHz image band, which fulfills minimum UMTS requirements. The chip size is 4×0.8 mm² and it has an active area of 0.15mm². Its power consumption is 69mW for a 2.6GHz operating clock frequency.

Keywords: delta-sigma modulation, digital transmitter, redundant arithmetic, software radio, RF, UMTS, switching-mode power amplifier, 90nm CMOS.

This thesis work has been performed in the Integrated Circuits Design Group / Microélectronique Silicium of the ISEN department of the Institut d'Electronique, de Microélectronique et de Nanotechnologies (IEMN), 41, bd Vauban, 59000 Lille, France.

Résumé

Génération numérique de signaux RF pour les terminaux de communication mobile par modulation delta-sigma

Les appareils de communications mobiles demandent de plus en plus un accès omniprésent aux réseaux sans fils à travers différents standards et bandes de fréquences. Les architectures radio-logicielles, conçues dans des technologies nanométriques avancées, sont très largement étudiées pour atteindre cet objectif. En particulier, l'interface entre les mondes numériques et analogiques/RF semble se déplacer au plus proche de l'antenne. Dans ce travail, une architecture de transmetteur numérique, basée sur la modulation $\Delta\Sigma$, est étudiée et un prototype de générateur de signaux RF numériques a été fabriqué pour prouver ce concept.

L'architecture proposée est construite autour de deux modulateurs $\Delta\Sigma$ passe-bas suréchantillonnés du 3^{ème} ordre qui fournissent un signal multiplexé sur 1 bit à haute cadence, qui code directement le signal RF dans le domaine numérique. Les fonctions de transfert des modulateurs comportent une mise en forme du bruit de quantification pour le déplacer en dehors de la bande d'émission du standard considéré, permettant ainsi d'atteindre un rapport signal-à-bruit élevé et peu de distorsion dans la bande d'émission. La séquence de sortie peut ensuite être appliquée à l'entrée d'un amplificateur de puissance commuté ayant une bonne efficacité.

Le standard UMTS a été choisi comme exemple d'application et un générateur de signaux RF numérique, fournissant un signal de sortie sur 1 bit à 7.8Géch/s a été réalisé dans une technologie 90nm CMOS. La cadence d'échantillonnage effective des modulateurs $\Delta\Sigma$ passe-bas est dans ce cas de 3.9Géch/s. Une optimisation approfondie au niveau architectural et au niveau logique a été obligatoire : une quantification des coefficients des modulateurs, une arithmétique redondante comprenant des signaux complémentaires, une quantification de sortie non exacte et une évaluation anticipée de la sortie ont été implémentés pour parvenir à la cadence désirée. Une logique dynamique différentielle sur 3 phases d'horloge, générées par une DLL, a été utilisée au niveau circuit.

Le circuit intégré du transmetteur prototype démontre une fonctionnalité complète jusqu'à une fréquence d'horloge de 4GHz, permettant ainsi d'atteindre une bande passante maximum de 50MHz autour d'une fréquence porteuse de 1GHz avec une puissance de sortie en pic de 3.1dBm. Si la première bande image est utilisée, la bande d'émission peut être déplacée jusqu'à 3GHz, avec cependant une puissance de sortie réduite à cause de la fonction de mise en forme du sinus cardinal. Avec une fréquence d'horloge de 2.6GHz et un canal WCDMA de 5MHz modulé autour d'une fréquence porteuse de 650MHz, la puissance de canal en sortie est de -3.9dBm et 53.6dB d'ACLR sont obtenus. Avec les mêmes paramètres, la puissance du canal en sortie est de -15.8dBm et un ACPR de 44.3dB est atteint pour la bande image à 1.95GHz, ce qui rentre dans les spécifications UMTS. Les dimensions du circuit sont 4×0.8mm², tandis que l'aire active est de 0.15mm². La consommation du circuit est de 69mW sous 1V pour une fréquence d'horloge de 2.6GHz.

Mots-clés : modulation delta-sigma, transmetteur numérique, arithmétique redondante, radio logicielle, RF, UMTS, amplificateur de puissance commuté, CMOS 90nm.

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Glossary of acronyms

$\Delta\Sigma$	Delta-Sigma
3G	Third Generation of mobile phone wireless systems
4G	Fourth Generation of mobile phone wireless systems
ACLR	Adjacent Channel Leakage Ratio
ACPR	Adjacent Channel Power Ratio
ADC	Analog-to-Digital Conversion/Converter
AWG	Arbitrary Waveform Generator
BAW	Bulk Acoustic Wave
BP	BandPass
BPF	BandPass Filter
BS	Borrow-Save
BSD	Binary Signed-Digit
C2	Two's complement
CDMA	Code Division Multiple Access
CDMA CDMA2000	Code Division Multiple Access Code Division Multiple Access 3G US standard
CDMA CDMA2000 CIC	Code Division Multiple Access Code Division Multiple Access 3G US standard Cascade Integrator Comb
CDMA CDMA2000 CIC CIFB	Code Division Multiple Access Code Division Multiple Access 3G US standard Cascade Integrator Comb Cascade of Integrators with FeedBacks
CDMA CDMA2000 CIC CIFB CIFF	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwards
CDMA CDMA2000 CIC CIFB CIFF CLA	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwardsCarry-LookAhead adder
CDMA CDMA2000 CIC CIFB CIFF CLA CLK	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwardsCarry-LookAhead adderClock
CDMA CDMA2000 CIC CIFB CIFF CLA CLK CMOS	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwardsCarry-LookAhead adderClockComplementary Metal Oxide Semiconductor
CDMA CDMA2000 CIC CIFB CIFF CLA CLK CMOS CORDIC	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwardsCarry-LookAhead adderClockComplementary Metal Oxide SemiconductorCoordinate Rotation Digital Computing
CDMA CDMA2000 CIC CIFB CIFF CLA CLK CMOS CORDIC CPL	Code Division Multiple AccessCode Division Multiple Access 3G US standardCascade Integrator CombCascade of Integrators with FeedBacksCascade of Integrators with FeedForwardsCarry-LookAhead adderClockComplementary Metal Oxide SemiconductorCoordinate Rotation Digital ComputingComplementary Pass-transistor Logic
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DAC	Digital-to-Analog Conversion/Converter
dBc	Power referenced to a carrier power, expressed in decibels
dB _{FS}	Power referenced to a full-scale sine wave, expressed in decibels
dBm	Power referenced to 1 milliWatt, expressed in decibels
DC	Direct Current
DCO	Digitally Controlled Oscillator
DCS	Digital Cellular System
DDR	Double Data Rate
DECT	Digital Enhanced Cordless Telecommunications
DLL	Delay Locked Loop
DPCCH	Dedicated Physical Control CHannel
DPDCH	Dedicated Physical Data CHannel
DPL	Double Pass-transistor Logic
DRFC	Digital-to-RF Converter/Conversion
DS-CDMA	Direct-Sequence Code Division Multiple Access
DS-SS	Direct-Sequence Spread Spectrum
DSP	Digital Signal Processing/Processor
DUT	Device Under Test
ENOB	Effective Number Of Bits
ETSI	European Telecommunications Standards Institute
EVM	Error Vector Magnitude
FA	Full-Adder
FAMMP	Minus-Minus-Plus Full-Adder
FAPPM	Plus-Plus-Minus Full-Adder
FDD	Frequency Division Duplex
FFT	fast Fourier Transform
FIR	Finite Impluse Response
FH-SS	Frequency Hopping Spread Sprectrum
FPGA	Field Programmable Gate Array

FS	Full-Scale
GSM	Global System for Mobile communications
GS/s	Giga Samples per second
HA	Half-Adder
HiperLAN2	High Performance Radio Local Area Network type 2
HPSK	Hybrid Phase Shift Keying
IEEE	Institute of Electrical and Electronics Engineers
IEEE802.11	Technology associated with WLAN defined by IEEE
IEEE802.20	Technology associated with MBWA defined by IEEE
IC	Integrated Circuit
IF	Intermediate Frequency
INS	Integral Noise Shaping
IS-95	Interim Standard 95 (known as cdmaOne)
ISI	Inter-Symbol Interference
I/O	Input/Output
LO	Local Oscillator
LP	LowPass
LPDSM	Low-Pass Delta-Sigma Modulator
LPF	LowPass Filter
LSB	Least Significant Bit
MAC	Medium Access Control
MBWA	Mobile Broadband Wireless Access
Mc/s	Mega chips per second
MCC	Manchester Carry Chain
MS/s	Mega Samples per second
MSB	Most Significant Bit
MUX	Multiplexer
NMOS	N-type Metal Oxide Semiconductor
NTF	Noise Transfer Function

PA	Power Amplifier
PAPR	Peak-to-Average Power Ratio
РСВ	Printed Circuit Board
PHS	Personal Handy-phone System
РНҮ	PHYsical layer
PMOS	P-type Metal Oxide Semiconductor
PN	Pseudo-Noise
PWM	Pulse Width Modulation
QPSK	Quaternary Phase Shift Keying
RCA	Ripple Carry Adder
RF	Radio Frequency
RLC	Radio Link Control
RRC	Radio Ressource Control
RRC	Root-Raised Cosine
RS	Reset-Set
RX	Reception
S/P	Serial-to-Parallel
SD-r	Signed-Digit adder in base r
SDR	Software Defined Radio
SFDR	Spurious Free Dynamic Range
SiP	System in Package
SNDR	Signal-to-Noise and Distortion Ratio
SNR	Signal-to-Noise Ratio
SRC	Sample Rate Conversion/Converter
STF	Signal Tranfer Function
SoC	System on Chip
TDCDMA	Time Division Code Division Multiple Access
TDD	Time Division Duplex
TSPCFF	True Single-Phase Clock Flip-Flop

TX	Transmission
UE	User Equipment
UMTS	Universal Mobile Telecommunications System
VHDL	Very high speed IC Hardware Description Language
WCDMA	Wideband Code Division Multiple Access
Wi-Fi	Wireless Fidelity
Wimax	Worldwide Interoperability for Microwave Access
WLAN	Wireless Local Area Network

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Introduction

"Welcome to the machine" (Pink Floyd)

In the 2005 edition of the European Solid-State Circuit Conference (ESSCIRC) joint with the European Solid State Device Research Conference (ESSDERC), a rump session entitled "Where will the revolutionary solutions come from: Technology or Design?" has brought together eight international experts in technology/devices and advanced design to argue on the perspectives for future solutions. The final answer was that technology and design together will make barriers fall. As a member of the Integrated Circuits Design Group of the Institut d'Electronique, de Microélectronique et des Nanotechnologies (IEMN), my work is devoted to enhance the design knowledge and to probe further into state-of-the-art advanced design techniques. In this thesis work, I try to conceive, with a given technology, the most powerful and innovative system by bringing design solutions.

The application field of this work is the mobile communications, especially the transmission side. This field offers great challenges, as every new standard comes with more and more restrictive requirements. Moreover, as almost all hardware solutions, power consumption and integration are always crucial factors. From this point of view, each research team tries to tend to the chip that will integrate most functional blocks, consume less and fit with the maximum number of standards. We place ourselves in this context, in which we would like to demonstrate the feasibility and the flexibility of an innovative digital chip with potential industrial applications.

Concretely, this research work introduces an all-digital transmitter architecture able to replace with a marked improvement the front-end circuits in mobile communications terminals. This architecture takes advantage of the oversampled delta-sigma ($\Delta\Sigma$) modulation,

able to quantify a digital word into a 1-bit high-speed stream without losing the information inside excessive quantization noise. The issue is by far the huge computations needed for this operation. Innovative techniques, coming from electronic or other domains, have been developed to overcome the blocking points. Huge efforts have been made to design a full 90nm CMOS chip to demonstrate the proposed concept.

Here is the chapter organization.

The first chapter presents the background of this thesis. It highlights the needs to reach ideal software radio terminals. Then, the evolution of transmitters, from nowadays analog implementations to the digital RF case is detailed, with emphasis on major publications. For the demonstration of this digital RF transmitter prototype, we choose to focus on a particular standard and then to extend to other standards. European UMTS has been first chosen for its hard-to-fulfill requirements and its novelty. Major requirements for this standard are detailed in this section.

Chapter 2 presents the digital transmitter architecture. It explains architectural choices for the system core, including the delta-sigma modulators, the digital RF upconverter and the switching-mode power amplifier. Then, a global transmitter chain is proposed. Finally, a particular implementation of the transmitter chain for UMTS case is detailed for baseband processing, sample rate conversion and delta-sigma modulation blocks.

Chapter 3 deals with the $\Delta\Sigma$ modulator system design. In this chapter, techniques to achieve the computational effort are explained. First, an optimization for digital implementation is given. Then, redundant arithmetic is introduced after having stated the critical path and limitations of 2's complement adder architectures. The $\Delta\Sigma$ modulators design with this redundant arithmetic is fully covered. Finally, further necessary improvements, called non-exact quantization and output signal precomputation, are detailed.

Chapter 4 details the transistor level design of the whole transmitter. The global structure and layout is given in a first section. Then, each circuit block is detailed. The sample rate conversion block description gives an emphasis on the designed high-speed registers. $\Delta\Sigma$ modulator implementation is handled, focusing on the differential dynamic logic style. The $\Delta\Sigma$ layout strategy is also explained. Using this dynamic logic style leads to the description of the clock generation and distribution block, implemented by a DLL. Finally, the digital mixer and output stages structures are presented.

Chapter 5 gives an overview of the test setups and measurement results and analyzes the obtained results. Two 90nm CMOS chip have been designed and tested. The first one was

not fully functional but a lot of valuable information could have been gathered. After redesign and fabrication, the second chip was operational and has been thoroughly tested. For each one, test hardware and assembly is described. Then, the measurement results are given, analyzed and compared with other literature results.

Finally, a conclusion will sum up this work with an emphasis on parallel works, reconfigurability perspectives and future directions.

CHAPTER 1 BACKGROUND

To introduce the background of this thesis work, the concept of software defined radio will be presented. Then, a state-of-the-art in transmitter architecture is established, starting from the analog RF implementation and going to the digital RF implementation. The objective of this work is to demonstrate a digital RF transmitter based on delta-sigma modulation. In order to work with real specifications, UMTS standard has been chosen for demonstration. Requirements for this standard will be stated in order to clarify architecture choices and to evaluate the transmitter performances.

1.1 Software defined radio

1.1.1 Universality of RF transmitters

Imagine a mobile phone able to operate all over the world and to travel on most of the wireless networks. This kind of terminal should become a reality with the growth of software-defined radio (SDR). This technology lets us manufacture flexible radios, able to adapt themselves to different standards by simply updating a firmware.

Indeed, an emitter creates electromagnetic waves on an antenna, with specific attributes related to the standard on which it operates. Nowadays, this work is performed by several specialized chips, programmed once and for all to compute signals in the targeted frequency band, according to a defined standard. As a result, those different radio terminals are not compatible and thus limited to their own specificity.

Software defined radio (also called "reconfigurable radio" or "intelligent radio") uses global programmable chips, able to switch from a standard to another by choosing the appropriate software. A SDR mobile phone should then access all networks used in the world. Utility of SDR handsets becomes more visible as standards proliferate. Those various standards can be divided into several types [1]:

- Second generation digital radio wireless systems (GSM and DCS1800 in Europe, IS-95 in United States),
- Third generation digital radio wireless systems, such as UMTS (Europe), CDMA2000 (United States) or TD-SCDMA (China),
- Digital cordless systems, such as DECT or PHS,
- Broadband mobile-access systems (Wi-Fi, IEEE802.11, HiperLAN2...),
- Short-range systems, such as Bluetooth.

Moreover, new systems become available, such as 4G, Wimax or IEEE802.20 or even future 60GHz WLAN standards.

Software-defined radio finds its place in future radiocommunications architectures, on the way to universal transmitters.

1.1.2 Ideal software radio

The ultimate architecture for a software defined radio should be a digital multifunction signal processor (DSP), directly connected to an antenna through a digital-to-analog converter (DAC) for emission and an analog-to-digital converter (ADC), followed by a DSP, for reception (Figure 1-1).



Figure 1-1 Ideal software-defined radio transmitter

Progressive digitization of the analog blocks tends to bring the converters closer and closer towards the antenna [2, 3], starting from baseband digital processing, through intermediate frequencies (IF) digital processing, to tend toward RF digital processing (Figure 1-2). Nevertheless, relevant technical issues need to be solved in order to deploy software radio solutions. However, emergence of very high-speed digital signal processing makes the concept of SDR becoming a reality [4-6]. From this point of view, this work tries to

demonstrate the feasibility of an all-digital RF transmitter architecture, using digital deltasigma modulation and switching-mode power amplifiers.



Figure 1-2 Toward RF digital processing and software radio

1.2 State-of-the-art in transmitter architectures

The state of the art presented in this subpart is a comprehensive, but not exhaustive, picture of digital transmission architectures at the beginning of this work in 2004. It depicts the general trends for implementing transmission architectures. Later work and results from other research teams will be discussed in the conclusion.

It will be shown that, following the evolution of transmission architectures, the global trend is to digitize the transmission chain. To visualize this trend, a color code has been employed on the different figures. All digital parts appear in green, whereas analog ones are in red. An intensity code is also used to separate baseband blocks (very light color) from RF parts (strong ones). IF processing blocks appear in an intermediate intensity. A cutting edge in RF transceiver architectures for WCDMA has been made in 2001 in [7].

1.2.1 Analog front-end architectures

Traditionally, transmitter architectures are almost exclusively analog in all front-end parts. Digital blocks are only found in baseband and digital-to-analog conversion is made with baseband DACs at low sample rates. Then, two implementations exist:

Most of the existing transmitters are based on a two-step up-conversion architecture (Figure 1-3), called heterodyne transmitter. An interesting implementation can be found in

[8]. The signal is first up-converted to an intermediate frequency, filtered, up-converted to the radio frequency, amplified and finally filtered again before emission on the antenna. The filtering at IF or RF cannot be done with active structures, which makes it very difficult to completely integrate transmitters. Furthermore, two different local oscillator signals are needed.



Figure 1-3 Heterodyne transmitter architecture

An obvious solution would be to use only a direct up-conversion architecture, where the baseband signal is directly modulated to RF (Figure 1-4). However, the direct conversion or homodyne transmitter suffers from low performances at low output power and from a phenomenon called LO-pulling. The oscillator in the frequency synthesizer operates at the same frequency as the power amplifier in the transmitter. Due to the limited amount of isolation achievable, the transmitted output signal will couple to the oscillator and seriously degrade its performances. Moreover, the quadrature upconverter suffers from a higher IQ mismatch than in heterodyne transmitters, as it is now operating at RF. Examples of homodyne implementations can be found in [9].



Figure 1-4 Homodyne transmitter architecture

1.2.2 Digital IF architectures



Figure 1-5 Digital-IF transmitter architecture

An evolution from previous implementations is the Digital-IF architecture, in which the digital signal is converted to analog after IF quadrature upconversion, generally using a $\Delta\Sigma$ DAC (Figure 1-5). This architecture benefits from better silicon integration, ideal IQ matching and thus a lower error vector magnitude.

An interesting implementation is presented in [10] and [11], which details a digital quadrature modulator, associated with a 1-bit $\Delta\Sigma$ modulator and a current-mode DAC to replace analog IF upconversion (Figure 1-6). The 0.13µm CMOS chip can work with a 700MHz clock frequency to address an IF frequency of 175MHz. It consumes 139mW at 1.5V and occupies 5.2mm².





In [12], this kind of architecture is implemented using a second-order-hold DAC in 0.25µm SiGe BiCMOS (Figure 1-7). The multi-bit delta-sigma DAC is working at 250MHz. Analog Variable Gain Amplifier (VGA) and mixer stages are integrated into the chip to deliver an output power of 5dBm, while consuming 180mW at 3V. However, this structure is working with current-mode DACs, which limits, at low voltage, the maximum power that can

be delivered to a load. Such structures are incompatible with more efficient class-S power amplification.



Figure 1-7 Conceptual block diagram of the digital-IF heterodyne transmitter from [12]

1.2.3 Digital RF architectures



Figure 1-8 Digital RF transmitter chain

Advances and maturity of deep submicron CMOS technologies enable the DAC to reach higher sample rates. So, the idea of a digital RF implementation is rising [4, 5, 13]. It deletes all analog mixers and replaces them by a direct-digital quadrature upconverter and a switching-mode power amplifier driven by, e.g., a $\Delta\Sigma$ -modulated high-speed signal (Figure 1-8 and Figure 1-9). An advantage is the high efficiency of the output stages. At the time of this work, no IC implementation of this kind of structures can be reported. However, ideas for such architectures are presented in several publications.



Figure 1-9 DSP-based wireless transmitter architecture from [5]

The fundamental concept is to use bandpass $\Delta\Sigma$ modulation to produce a high-speed digital signal driving a switching PA:

- [14] demonstrates such a digital transmission chain by experimentally generating the produced bit-stream with a pattern generator and a serializer.
- [6, 15-17] present the concept and show simulation and measurement results for relatively low output frequency, extrapolating simulations to higher output frequencies.

Another method for digitally generating an RF signal is termed "Quadrature Integral Noise Shaping" (INS) and uses PWM coding scheme to generate baseband IQ complex signals. References [18] and [19] detail related architectures.

Moreover, an interesting paper [20] proposes to drive a DCO (Digitally Controlled Oscillator) with a $\Delta\Sigma$ -modulated signal to generate the phase information and to regulate the power amplifier amplitude to control the amplitude information.

Digital generation of RF signals by $\Delta\Sigma$ modulation and switched power amplifiers seems to be the most promising implementation in terms of configuration possibility and software radio convergence.

1.3 UMTS standard specifications

The Universal Mobile Telecommunications System (UMTS) in Frequency Division Duplex (FDD) mode will be first considered in order to emphasize the concept studied in this work. UMTS is the standard chosen for 3G mobile communications in Europe. Specifications for the UMTS standard are defined by ETSI [21]. These specifications cover all aspects of transmission and reception for handset terminals. As an introduction to UMTS, only aspects that concern the definition of the global transmitter to be designed are given hereafter. Furthermore, the extension of the highlighted approach to other standards is still under investigation and will be discussed in the conclusion.

1.3.1 Introduction to UMTS

1.3.1.1 Protocol layers

The architecture of the UMTS radio interface is structured into layers, in which protocols are based on the first three layers of the Open Systems Interconnection (OSI) reference model [22], as illustrated in Figure 1-10:

- The first layer is the physical one, devoted to transmit and receive data over the channel.
- The second layer is the medium access control (MAC), which is able to control the data sent and received and to retransmit error packets. This layer provides data and information to the physical layer.
- The third layer is the radio resource control (RRC). It controls and maps the connections.



Figure 1-10 Radio interface protocol structure [22]
In the following sections, only transmitter physical layer, starting from the baseband signals provided by the MAC layer will be considered.

1.3.1.2 Access mode and frequency allocation

The frequency sharing technique adopted for UMTS is the Code Division Multiple Access (CDMA): data from different users coexist within the same channel and spread spectrum modulation is used to attribute a specific code to each user. Two methods allow spreading signals: the Frequency Hopping (FH-SS) technique and the Direct-Sequence one (DS-SS) [23]. Since only the DS-SS technique is adopted in UMTS, it is shortly detailed hereafter. Direct-Sequence spread spectrum consists in multiplying the signals symbols by a specific pseudo-random binary sequence. CDMA systems using direct sequence spreading are called DS-CDMA. For UMTS, information is spread over about 5MHz, hence it is called WCDMA (W is for Wideband). Two duplex modes exist in UMTS, Frequency Division Duplex (FDD) and Time Division Duplex (TDD).

Figure 1-11 gives a comparison between spectrum access techniques used in GSM and UMTS. For GSM, the whole frequency band is split into 200kHz wide channels multiplexed in time between emission and reception. For UMTS in TDD mode, information is spread over 5MHz channels and separated per code. The transmitter and the receiver are working in half-duplex. Time slots are alternatively allocated for emission and reception. FDD mode also uses CDMA but the transceiver is working in full-duplex. The reception band is placed away from the emission band (not shown in the figure). The two front-end architectures operate at the same time, using a duplexer.



Figure 1-11 Examples of access modes for GSM, UMTS TDD and FDD

The study is focused on FDD mode in which uplink and downlink are separated in two frequency bands, instead of separated time slots. UMTS FDD operates on two 60MHz bands, separated by 190MHz. The uplink uses 1920-1980MHz band while the downlink band is located between 2110 and 2170MHz. Our interest only goes to the uplink path, from the user terminal to the base station.

Inside the 1920-1980MHz band, twelve 5MHz wide channels exist. Chip rate is 3.84Mc/s (Mega chips/second), but data rate is tied to the spreading factor. Channels are larger than the relative chip rate due to the roll-off factor (generally stated α) of the Root-Raised Cosine (RRC) filter used. In UMTS, the roll-off factor is equal to 0.22, thus the channel bandwidth is equal to chip rate×(1+ α) = 4.68MHz. A channel is shown on Figure 1-12, illustrating the effect of the root-raised cosine filter. The modulation used by UMTS is the Quaternary Phase Shift Keying (QPSK).



Figure 1-12 Example of a RRC-shaped UMTS channel

1.3.2 UMTS specifications for transmitters

Specifications on spectrum emissions are given at the antenna connector. It will be considered that the antenna connector is loaded by a nominal single ended 50 Ω impedance. These specifications lead to a spectrum emission mask and out-of-band spurious emissions constraints as explained in the following sections.

1.3.2.1 Spectrum emission mask

The spectrum emission mask applies to frequencies, which are between 2.5 MHz and 12.5 MHz away from the User Equipment (UE) centre carrier frequency (related to the chosen channel). The out-of-channel emission is specified relative to the RRC filtered mean power of the UE carrier. Table 1-1 shows requirements for UMTS spectrum emission mask and Figure 1-13 translates the requirements on a graph.

	Minimum requirement (Note 2)		Magguramont
Δf in MHz (Note 1)	Relative requirement	Absolute requirement	bandwidth
$2.5 \le \Delta f \le 3.5 \text{ MHz}$	$-35-15\left(\frac{\Delta f}{MHz}-2.5\right)dBc$	-71,1 dBm	30 kHz
$3.5 \le \Delta f \le 7.5 \text{ MHz}$	$-35-1\left(\frac{\Delta f}{MHz}-3.5\right)dBc$		
$7.5 \le \Delta f \le 8.5 \text{ MHz}$	$-39-10\left(\frac{\Delta f}{MHz}-7.5 ight)dBc$	-55,8 dBm	1 MHz
$8.5 \leq \Delta f \leq 12.5 \text{ MHz}$	-49 dBc		

Note 1: Δf is the separation between the carrier frequency and the center of the measurement bandwidth.

Note 2: The minimum requirement is calculated from the relative requirement or the absolute requirement, whichever is the higher power.





Figure 1-13 UMTS spectrum emission mask (related to a 1MHz measurement bandwidth)

1.3.2.2 Adjacent Channel Leakage Power Ratio

Another parameter is defined to obtain the desired spectrum requirement. Adjacent Channel Leakage power Ratio (ACLR) is the ratio of the RRC filtered mean power centered on the assigned channel frequency to the RRC filtered mean power centered on an adjacent channel frequency. If the channel power is greater than -50dBm then the ACLR specifications in Table 1-2 should be met.

Adjacent channel frequency relative to assigned channel frequency	ACLR Limit
+ 5 MHz or – 5 MHz	33 dB
+ 10 MHz or – 10 MHz	43 dB

Table 1-2 UMTS ACLR

1.3.2.3 Spurious emissions

In addition to in-band requirements, UEs are not authorized to spread power everywhere. Some frequency bands, used in other standards, are sensitive to perturbations. To overcome this, maximum spurious emission levels are defined in determined frequency bands. Out-of-band requirements are plotted on Figure 1-14 between 900MHz and 2.2GHz. This plot corresponds to normalized power emission in dBm/Hz over standards frequency bands, as defined by the ETSI (Table 1-3). On this qualitative plot, proportionality is not respected. However, this plot is relevant for visual understanding.

Receive band specifications (RX bands) are the hardest ones to meet. For the GSM900 band, a maximum of -129dBm/Hz is required. For the DCS1800, -126dBm/Hz is the limit of spurious emission. The RX band of UMTS is placed 190MHz higher than transmit band (TX band). The maximum allowed level is -129dBm/Hz at the antenna. However, an UMTS terminal is working in full duplex using a duplexer. That means the UE is transmitting and receiving data at the same time. That's the reason why the RX band requirement must be lowered down to -183dBm/Hz. UMTS RX and DCS1800 RX specifications are the most demanding ones, as they are very close to the UMTS transmit band (TX band).



Figure 1-14 UMTS spurious requirements

Frequency Band (MHz)	Measurement Bandwidth	Requirement (dBm)
0,009 - 0,15	1 kHz	
0,15 - 30	10 kHz	-36
30 - 860	100 kHz	
860 - 895	3.84 MHz	-60
895 - 921	100 kHz	-36
921 - 925	100 kHz	-60
925 - 935	3.84MHz	-60
935 - 960	100 kHz	-79
960 - 1000	100 kHz	-36
1000 - 1805	1 MHz	-30
1805 - 1844,9	100 kHz	-71
1844,9 - 1880	3.84 MHz	-60
1880 - 1884,5	1 MHz	-30
1884,5 - 1919,6	300 kHz	-41
1919,6 - 2110	1 MHz	-30
2110 - 2170	3.84 MHz	-60
2170 - 2620	1 MHz	-30
2620 - 2690	3.84 MHz	-60
2690 - 12750	1 MHz	-30

Table 1-3 UMTS spurious emissions table

1.3.2.4 Error Vector Magnitude

Finally, UMTS norm defines quality criterions. A useful one is the Error Vector Magnitude (EVM) measurement. It is an evaluation of the difference between a reference data signal and the measured data signal. EVM is defined as the square root of the ratio between

the error vector mean power and the reference signal mean power, expressed in percentage. Figure 1-15 explains on an IQ diagram the phase and amplitude errors associated with the EVM definition. In normal conditions and for an output power greater than -20dBm, EVM must be lower than 17.5%. However, typical performance of mobile transmitters is an EVM of about 7%.





1.4 Conclusion

The work presented in this thesis is devoted to software radio, trying to approach as much as possible an ideal implementation. In a first study, the European standard for 3G communications (UMTS) is chosen for its hard-to-fulfill requirements. Main UMTS specifications, directly related to our work, have been detailed.

Nowadays, transmitters in mobile handsets are mainly analog. The trend to digitize all processing blocks brings us to find new ways of implementing transmission chains. An architecture based on digital RF $\Delta\Sigma$ modulators, digital quadrature upconverters and switching-mode power amplifiers has been determined as a good candidate to enable digital radio and will be discussed in more detail in the next chapter.

CHAPTER 2 DIGITAL TRANSMITTER ARCHITECTURE

The digital RF transmitter architecture, as presented in paragraph 1.2.3, can be implemented, at system level, in several different ways. In the first section of this chapter, two possible system architectures are presented and the choices made in this work justified. The more detailed structure of all sub-blocks in the selected system architecture is presented in the subsequent sections.

2.1 Global transmitter architecture

2.1.1 Transmitter architecture and frequency planning



Figure 2-1 Digital transmitter architecture. f_{chip} is the chip rate, f_c the carrier frequency and f_s the sampling frequency.

The global function of the digital transmitter is to convert a multi-bit digital I/Q baseband signal at baseband sampling rate (chip rate) into a digital 1-bit RF signal at a very

high sampling rate that can be fed to a switching power amplifier. The underlying fundamental principles are oversampling and noise-shaping. Delta-sigma modulators are used to shape the noise in an appropriate way to move it out of the targeted transmit band. The global architecture is presented on Figure 2-1. An analog filter is then necessary at the output of the digital transmitter to remove the high out-of-band quantization noise. If a fixed frequency analog filter is used, the modulator must provide low quantization noise over the full transmit band of the targeted standard for all carrier frequencies. In a simple direct-conversion architecture, the sampling frequency would be proportional to the carrier frequency. The worst-case situations are then the channels situated at the edges of the transmit band (Figure 2-2a). In fact, for a low quantization noise for all possible channels inside the standard band, the $\Delta\Sigma$ modulator bandwidth must be twice the width of the transmit band, thus increasing the noise shaper requirements.



Figure 2-2 Modulator output spectrum for channels at the lowest band edge for (a) direct conversion and (b) two-step conversion

To relax the requirements on the noise shaper, a two-step upconversion architecture has been chosen (Figure 2-3). The RF sampling frequency is fixed, and the center of the noise-shaper bandwidth is placed on the center of the standard transmit band, independently of the actual channel used for the transmit path (Figure 2-2b). In the first step the complex base-band signal is moderately oversampled and then placed on the appropriate channel by a digital multiplier. For UMTS, the corresponding 12 channel center frequencies are stated in Table 2-1 and are given by:

$$F_{channel} = \pm (2.5MHz + k \times 5MHz), k = 0,1,2,3,4,5$$
 Eq. 2-1



Figure 2-3 Two-step upconversion transmitter architecture. *L* is a factor dependent over the chosen standard.

Channel number	Channel center frequency	
1	-27.5 MHz	
2	-22.5 MHz	
3	-17.5 MHz	
4	-12.5 MHz	
5	-7.5 MHz	
6	-2.5 MHz	
7	2.5 MHz	
8	7.5 MHz	
9	12.5 MHz	
10	17.5 MHz	
11	22.5 MHz	
12	27.5 MHz	

Table 2-1 Channel center frequencies for UMTS standard

In the second step the signal is again oversampled up to the RF sampling frequency, transposed to RF and finally quantized with a bandpass 1-bit noise-shaper.

Upconversion of the digital IF signal to RF is achieved by a digital image-reject mixer as shown in Figure 2-3. In the general case, two multipliers and a summer are required, all operating at the RF sampling frequency. By choosing the RF sampling frequency equal to 4 times the center frequency of the transmit band, the operation is however greatly simplified. In that case, the 90° phase shifted I and Q Local Oscillator (LO) signals can be represented by the following sequences [24]: $LO_I:$ 1, 0, -1, 0 $LO_Q:$ 0, 1, 0, -1

As it can be seen, at any time one of the two LO signals is equal to zero. Therefore, the adder in the mixer can be replaced by a simple multiplexer, selecting the I channel on odd periods and the Q channel on even periods. Furthermore, the multiplications are replaced by a simple change of the sign of the digital data, eliminating multipliers entirely. The digital image-reject mixer reduces to the function shown in Figure 2-4. The digital RF output stream is simply the following sequence:

$$RF_{out} = \{I(n), Q(n+1), -I(n+2), -Q(n+3)\}, n = 0, 4, 8, 12, \dots$$
 Eq. 2-2



Figure 2-4 Digital mixer operation. The sample rate is $4 \times f_c$ and n = 0,4,8,12,...

A major drawback of this architecture is however the fact that the ratio of the IF to the RF sampling frequencies is not necessarily integer, as one is related to the chip rate and the other to the center frequency of the standards transmit band. A sophisticated multi-rate digital interpolator is in principle necessary to accomplish this sample-rate conversion. This can however be avoided through careful frequency planning. By slightly offsetting the RF sampling frequency, an integer ratio can be reached. The corresponding frequency offset on the channel center frequency must simply be corrected in digital baseband by offsetting the channel center frequencies by the opposite amount. In the case of UMTS, the chip rate is 3.84MHz, while the exact center frequency is 1950MHz, yielding a ratio of 507,8125. As an example, when setting the RF center frequency to 512 times the chip rate, it is offseted by

+16.08MHz with respect to the exact center of the transmit band. For UMTS, the corresponding 12 channel center frequencies would then be (Table 2-2):

$$F_{channel} = \pm (2.5MHz + k \times 5MHz) - 16.08MHz, k = 0,1,2,3,4,5$$
 Eq. 2-3

Channel number	Channel center frequency	
1	-43.58MHz	
2	-38.58MHz	
3	-33.58MHz	
4	-28.58MHz	
5	-23.58MHz	
6	-18.58MHz	
7	-13.58MHz	
8	-8.58MHz	
9	-3.58MHz	
10	1.42MHz	
11	6.42MHz	
12	11.42MHz	

Table 2-2 Offseted channel center frequencies for UMTS standard

Another advantage of fixed RF sampling frequency is relaxed phase-noise requirements on the RF sampling clock. This clock plays the role of the local oscillator once the output signal is interpreted in the analog domain. Critical specifications are related to the near-by receive bands because of spurious emission requirements, that again must be met in the worst-case conditions corresponding to the lowest and highest channel center frequencies. In the fixed sampling-frequency architecture the margins from the clock frequency to the critical bands are increased by 27.5 MHz for UMTS.

To illustrate this relaxed requirements on the local oscillator phase noise, VCO phase noise requirements from IST European projects MELODICT [25] and MOBILIS [26] are given in Table 2-3. In MELODICT project, clock phase noise values are derived from the standard specifications. In MOBILIS project, an architecture similar to the one presented here is used. Therefore, phase noise requirements are relaxed. The phase noise for a 40MHz offset is almost equal to the phase noise specification in MELODICT project for a 10-15MHz offset.

Offset (MHz)	Phase noise level in MELODICT project	Phase noise level in MOBILIS project
5	-99.2dBc/Hz	-
10	-117dBc/Hz	-
15	-120dBc/Hz	-
40	-148dBc/Hz	-119dBc/Hz

Table 2-3 RF clock frequency phase noise requirements

2.1.2 Digital upconversion and noiseshaping architecture

Two architectures can achieve the required functions of quantizing the input signal to a 1-bit data stream and upconvert the baseband signal to the desired RF band. These architectures are presented on Figure 2-5. In the first one, a bandpass $\Delta\Sigma$ modulator clocked at $4 \times f_c$ is placed after the digital up-conversion to produce the 1-bit digital output stream. In the second one, two lowpass $\Delta\Sigma$ modulators, also clocked at $4 \times f_c$, are placed on I and Q paths prior to the upconversion of the signal [27].



Figure 2-5 Possible architectures for noise shaper and upconverter: a) Bandpass $\Delta\Sigma$ modulator; b) Lowpass $\Delta\Sigma$ modulators.

In terms of complexity, the two architectures are approximately equivalent. The digital mixer is simpler in the second architecture, as it operates only on 1-bit signals. The complexity of the $\Delta\Sigma$ modulators is equivalent, as the order of the bandpass $\Delta\Sigma$ modulator is twice the order of the low-pass $\Delta\Sigma$ modulators for the same noise-shaping at the output. However, the second architecture offers further margins for optimization. If we further refine the analysis, it can be noticed that the input of the digital I/Q mixer actually samples only odd samples in I path and only even samples in Q path. If we do not produce the unnecessary samples, the effective sampling rate of the delta-sigma modulators in I and Q paths is only half of the RF sampling rate (Figure 2-6). The $\Delta\Sigma$ modulators are working in quadrature for proper operation. This will not only halve the power consumption of the modulators but also relax the requirements on the digital logic in the modulators as the cycle time is doubled. The combination of these two effects obviously is in favour of the second architecture, which clearly seems to be superior to the bandpass approach.



Figure 2-6 Simplified architecture if only one sample on two is computed inside the $\Delta\Sigma$ modulators. The Δ T delay is equal to $1/4 f_c$.



Figure 2-7 Frequency spectrum of the output of the digital upconverter when no interpolation is done on Q channel, showing the image that appears



Figure 2-8 Architecture if the $\Delta\Sigma$ modulators sampling clocks are synchronous.

In practice, however, we would like to use the same sampling instants for the two lowpass $\Delta\Sigma$ modulators in I and Q paths. If we simply process only odd samples in both I and Q paths, an image of the transmit channel appears in the RF spectrum because of the slight phase shift of the Q path (Figure 2-7). This can be solved in two ways. In a rigorous approach, the odd samples of the I path are delayed by one RF clock period, so that they now appear on the same clock edges as the even samples of the Q path (Figure 2-8).



Figure 2-9 Chosen architecture using a linear interpolation on Q channel. $\Delta {\rm T}'$ delay is equal to $1/2f_c$.

The drawback is that it is still necessary to oversample and interpolate the input signals to the RF sampling rate. An alternative approach is to linearly interpolate only the missing even Q samples from the odd ones. This globally reduces the sampling rate for all the circuitry prior to the digital mixer. The corresponding architecture and the effective image suppression in the RF spectrum are shown in Figure 2-9 and Figure 2-10.



Figure 2-10 Digital upconverter output spectrum. 8^{th} channel is chosen. OdB_{FS} refers to a full-scale sine wave.

2.1.3 Power amplifier and antenna filters

Output stages are not the main purpose of this work, but understanding of these blocks is essential in order to clarify implementation issues and to be aware of non-idealities and trade-offs to overcome. This part will focus on these issues.

The power amplifier, associated with antenna filters, is actually a 1-bit power digitalto-analog converter (DAC) [6, 15]. An advantage is the high linearity provided by the amplifier, as only two states exist. Switched-mode (class S) power amplifiers are also known to have a good theoretical efficiency.

2.1.3.1 Switching-mode power amplifier topology

The simplest switched-mode power amplifier is a simple inverter, large enough to provide the desired power, while working in triode region. Obviously, a growing chain of inverters must be implemented, to be able to drive the last one. Let's only consider the last inverter, presented on Figure 2-11. Theoretically, the efficiency is 100% when an ideal filter is inserted between the inverter and the load. All consumed power is directly provided to the load. Unfortunately, many losses degrade efficiency. Hence, total power is divided into useful load power, dissipated power in linear drain-to-source on-resistance, switching losses and direct path losses during transitions [28].



Figure 2-11 On the left, schematic of the output inverter; on the right, a diagram showing the repartition of the power supply

First, the R_{DS} on-resistance (in linear region) dissipates power as it acts as a resistive divider with R_{load}. R_{DS} is inversely proportional to the width *W* of the transistors. Next, switching losses are dependent of the value of C_{out}, proportional to *W* and the switching frequency. It is to note that in most cases, C_{out} will be overcome by be next driven gates or by the wiring capacitance (if the inverter is directly connected to a bonding pad, for example). Finally, during transitions, current is flowing directly from V_{DD} to ground, leading to direct path losses. Let's call t_{rf} the mean transition time for rise and fall, the direct path losses are frequency dependent and express as $V_{dd}.I_{peak}.t_{rf}.f$.

For high frequency activity, wasted power would become very large. Thus, there is a trade-off to make, when sizing the inverters, between staying in triode region to deliver the right current and voltage to the load and reducing the parasitic power consumption.

Another aspect to take into account when dealing with the output stages efficiency is the consumption of the inverter chain driving the last inverter. This consumption is process dependent, as it determines the number and the sizes of preceding stages.

Moreover, in the kind of architecture developed here, the useful information is bandlimited, so the square wave output of the power amplifier contains sinusoidal-shaped data in a band situated around the fourth of its sample rate. Thus, taking a sine wave example, the power contained by the useful information is 3dB lower than the power of the total square wave (holding all other frequencies). If we define the total efficiency as the ratio of the useful data power to the total consumed power, then this total efficiency falls down to 50%. A solution to avoid the amplification of unwanted frequencies, and so the associated useless consumption, is to design a filtering stage between the inverter output and the load. Filters must be wide enough not to distort content and sharp enough to correctly remove unwanted noise.

2.1.3.2 Power DAC non-idealities

The power amplifier is the limit between digital and analog world. Although it works on a single digital bit, it converts code information into an analog voltage representation. That's why we called it a power DAC. Inter-symbol interference (ISI) is the major distortion brought by the conversion. It comes from three major contributions.

First of all, the rise and fall times of the transitions will introduce a change in the energy contained in the signal. Figure 2-12a shows the effect of rise and fall times on the signal. For example, x_2 , x_4 and x_5 have the same logic value but different energies because of the next sample polarity. This difference doesn't appear with ideal edges. Study of this effect shows no alteration of the signal spectrum shape [29].



Figure 2-12 Inter-symbol interference: a) with symmetric fronts; b) with asymmetric fronts

The second effect is the edges asymmetry (Figure 2-12b). This study and other works explain that ISI is not created by rise and fall times, but by the unbalanced positive and negative symbols [30]. This asymmetry greatly degrades the frequency response by increasing

noise inside the bandwidth. Symmetry can be realized by using differential architectures. A comparison is shown in Figure 2-13, illustrating the benefit of a differential structure. Differential implementation deletes all ISI coming from this phenomenon and also offers the advantage of doubling the signal swing, thus quadrupling the output power. It obviously goes with more complex design and a larger silicon area.



Figure 2-13 Output spectra for ideal, single-ended and differential outputs

Finally, the last contribution is the jitter, defined as a misplacement of the edges related to the ideal sampling instant. Total jitter is decomposed in periodic jitter (also called sinusoidal jitter), caused by external deterministic noise sources, like switching power-supply noise, and in random jitter. Jitter increases the noise floor inside the bandwidth of interest. It mainly comes from clock oscillator phase noise.



Figure 2-14 Example of ACLR variations, for 5 and 10 MHz offset channels, related to random jitter variance.

An example of a random jitter study is presented in Figure 2-14, coming from an internal report on jitter study [31]. The ACLR requirements for UMTS, as stated in first chapter, are 33dB and 43dB for 5 and 10MHz offsets, respectively. Some headroom has been added so that the ACLR specification is set to 50dB. ACLR versus random jitter variance has been plotted to determine the maximum allowable jitter to reach the requirements. Here, the maximum jitter variance is 1.9ps to keep an ACLR greater than 50dB for both specifications.

2.1.3.3 Antenna filters

An issue in this kind of architecture using digital $\Delta\Sigma$ modulators is the resulting quantization noise outside the band of interest. This noise must be removed, especially in the frequency bands where other standards are operating. These constraints have been presented in the first chapter. The Figure 2-15 presents the system output digital spectrum, trasnposed to the antenna, if no filtering is done, to illustrate the demands in terms of filtering.



Figure 2-15 Digital RF output reported to the antenna (the standard measurement bandwidth has been respected (Table 1-3)) and UMTS spectrum requirements.

The filtering requirements are so stringent that simple LC filters cannot meet the requirements. Several filtering stages or very-high selectivity filters have to be designed. For example, Bulk Acoustic Wave (BAW) technology can bring the necessary filtering capacity for this kind of signal [32]. It is investigated in depth within the IST European MOBILIS project.

2.2 UMTS implementation case of the digital transmitter

2.2.1 Proposed digital transmission chain



Figure 2-16 Proposed transmitter chain

Figure 2-16 depicts the block diagram of the complete digital RF signal generator architecture considered throughout the rest of this work [33]. The delta-sigma ($\Delta\Sigma$) modulators and the digital upconverter provide a very high-speed 1-bit stream containing all in-band information. The oversampled $\Delta\Sigma$ modulators aim at keeping a high dynamic range within the bandwidth, and simultaneously at shaping the noise outside the band of interest. Since this block works with an oversampled signal, the signal from the baseband processing is upsampled to reach the $\Delta\Sigma$ modulators' sample rate.

This architecture tends towards an ideal software radio implementation by processing digital signals as close as possible to the antenna.

The following sections describe in details each block along the transmitter chain for the case of a UMTS implementation (except for the last three blocks, detailed earlier).

2.2.2 Baseband processing

The study of these blocks helps us in characterizing the system input signal. Indeed, a prior knowledge about information processed through the whole transmission chain is required before any simulation. The desired signal is an IQ modulated complex signal. Digital

processing blocks ensure its shaping [34, 35]. Figure 2-17 shows baseband blocks, while Figure 2-18 highlights the successive steps, depicted by encircled numbers, for generating the baseband signal.



Figure 2-17 Baseband processing blocks

First of all, two input signals called DPDCH and DPCCH (for Dedicated Physical Data Channel and Dedicated Physical Control Channel) contain information to transmit. It can be voice as well as communication data of any type. For generation purpose, these signals have been generated as pseudo-random binary sequences and then multiplied by orthogonal codes obtained by Walsh method. Orthogonal codes are useful to spread the signal spectrum over the desired bandwidth. At the output of this block, the binary sequences are sampled at the 3.84MS/s UMTS chip rate

Then, data scrambling allows separating users by assigning each one a different code and thus controls confidentiality of transmitted data [36]. PN-codes are used in UMTS to generate the HPSK complex scrambling sequence [37, 38].

Root-raised cosine (RRC) filtering is used to limit the spectrum of the coded information and to provide a properly shaped signal with preservation of its content. Moreover, inter-symbol interference is reduced by a filter such as a Nyquist filter. This digital filter enlarges the 3.84MHz signal with the 0.22 roll-off factor in order to have a 5MHz channel. It also introduces a delay equivalent to the half of the filter length. The output sample rate is twice the chip rate and equals 7.68MS/s.



Figure 2-18 Baseband signals at each step of the baseband processing

The proposed transmitter will compute the whole standard band (i.e. 60 MHz), instead of only a 5MHz wide shaped channel. Thereby, the 5MHz channel has to be placed, during baseband processing, on a chosen channel among the 12 available ones. It is done by oversampling stages followed by a CORDIC algorithm (Coordinate Rotation Digital Computing) [39]. In our case, the signal is oversampled 16 times to reach 122.88MS/s. This sample rate is chosen in order to avoid aliasing images of the channel from being too close to the channel of interest. That would not be acceptable for proper filtering of those images. The 122.88MS/s sample rate ensures images to fold relatively far away from the signal band.

The CORDIC rotator is a digital implementation of an upconverter, using exclusively adders and barrel shifters. CORDIC algorithm digitally places the channel on the appropriate IF carrier. Each channel is defined by a number *i* (from 1 to 12) and an associated centre frequency f_i which is a multiple of 2.5MHz situated between -30 and +30MHz plus or minus an offset corresponding to Table 2-2. Given the desired channel frequency, CORDIC algorithm is able to place the channel around this carrier with relatively low complexity.

All these baseband blocks have been modeled using MATLAB software to produce a flexible generation tool for further transmitter simulations. An example of a baseband output

signal is presented in Figure 2-19. The 9th channel, situated between 10 and 15MHz, is chosen here as an example.





2.2.3 Sample rate conversion

In the architecture considered here, the 122.88MS/s IQ signal has to be oversampled to 3.9GS/s, which is twice the carrier frequency of UMTS standard, in order to feed the oversampled delta-sigma modulator. The oversampling ratio is about 31.73. As explained earlier, the $\Delta\Sigma$ modulators sampling frequency would be adjusted to 3.93216GS/s for the oversampling ratio to be exactly 32. The channels would be offseted during baseband processing, thus the operation could be achieved by several half-band filters in cascade. Good image attenuation could be obtained but as sample rate increases, computational requirements become huge.

Since the digital delta-sigma modulator produces quantization noise outside the band of interest, non attenuated images by digital oversampling filters will fall below the quantization noise. This will happen provided the images are rather far from the centre of the band. Indeed, the quantization noise gets higher as frequency increases. It has been shown that a first half-band filtering with more than -70dBc attenuation on 122.888MHz images related to the channel power can relax requirements for other stages. Then, first-order interpolation by 16 can easily be realized at very low cost. Images at multiples of 245.76MHz never rise above the quantization noise. This is done by simply sample and hold the input signal at 16 times its rate. Good filtering at low sample rate relaxes computational effort at high sample rates. Figure 2-20 shows the chosen sample rate conversion architecture and highlights intermediate sample rates.



Figure 2-20 Sample rate conversion blocks

Figure 2-21 illustrates the implementation and shows the output spectrum for different configurations of data oversampling. The estimated delta-sigma modulator quantization noise is also drawn to choose the best solution, with following parameters:

- a) First-order interpolation by 32 (from 122.888MS/s to 3.9GS/s). One can notice that the image at 122.88MHz rises above the quantization noise;
- b) Half-band filtering followed by first-order interpolation by 16. This is a good trade-off between complexity and image attenuation.



Figure 2-21 Spectrums of the 3.9GS/s SRC output signals for the two configurations previously cited. In red, the estimated shaped quantization noise brought by the $\Delta\Sigma$ modulator.

2.2.4 Digital ΔΣ modulators

Interesting and detailed literature on oversampled delta-sigma modulation theory can be found in [40-44].

2.2.4.1 Lowpass ΔΣ modulator architecture

The bandwidth of the designed lowpass modulators has been enlarged to 100MHz for 20MHz guard bands on both sides of the 60MHz transmit band. The corresponding oversampling ratio is about 40. Lowpass $\Delta\Sigma$ blocks will be designed to fulfil the standard requirements for in-band required dynamic range. Hence, a third-order modulator is designed, with a 1-bit output data stream. It theoretically leads to approximately 80dB of maximum SNR.



Figure 2-22 (a) Pole-zero diagram (pole: x; zero: o); (b) NTF (red) and STF (green) of the generated $\Delta\Sigma$ modulator (frequency is normalized to f_s =3.9GHz); (c) zoom on the bandwidth (f_b =30MHz)

For architecture definition, we use the Delta-Sigma Schreier Toolbox for Matlab software [45], which is a tool for automatically generating standard $\Delta\Sigma$ architectures with optimal in-band zeros placement. A zero is centered at DC and the other ones are placed at the limit of the bandwidth. This has the effect of flattening the noise transfer function (NTF)

inside the bandwidth. Hence, the adjacent noise power for each channel will be approximately identical (Figure 2-22). It is to note that the signal transfer function (STF) introduces no inband attenuation.

The toolbox is able to translate the generated NTF and STF into a reliable architecture. The chosen architecture type is a cascade of integrators with feedbacks that feed back the quantized output to each integrator input. The configuration is presented on Figure 2-23. A global feedback with the g_1 coefficient creates the optimized zero location, at the limit of the transmit band. Coefficients for this architecture are summed up in Table 2-4. The output quantizer is working on two levels. Thus, it determines the sign of the computed signal. The output spectrum of this two-level output signal is plotted on Figure 2-24.



Figure 2-23 Third-order ΔΣ modulator architecture

Coeffi- cient	Value	Coeffi- cient	Value	
a ₁	0.1409457518558072	c_1	0.3166424812531309	
a ₂	0.2435218988625833	c ₂	0.1684863887945898	
a ₃	0.0945693329735421	g 1	0.0219599951361829	
b ₁	0.1409457518558072			

Table 2-4 Coefficients for the 3^{rd} -order $\Delta\Sigma$ modulator of Figure 2-23





For performance evaluation, we have considered classic parameters for $\Delta\Sigma$ modulators. The main parameter is the Signal-to-Noise and Distortion Ratio (SNDR), which is the SNR with distortion components (especially harmonics) taken into account as part of the noise. Another one is the Spurious Free Dynamic Range (SFDR). It is the available dynamic range between the maximum input power and the highest spurious power (most of the time the 3rd harmonic).

For the above architecture we obtain SNDR = 76.6dB and SFDR = 87.2dB. The former value leads to the calculation of an Effective Number Of Bits (ENOB) of 13, which is the in-band dynamic associated with the calculated SNDR. These parameters are obtained by putting a 10MHz sinusoidal signal at the input with the maximum stable amplitude (-3dB_{FS}). SNDR is relatively stable when applying sinusoids at other frequencies, due to the flatness of the quantization noise.

When applying an UMTS channel-shaped signal, we have access to the Adjacent Channel Leakage Ratio (ACLR) parameter for 5 and 10MHz offsets, which is the ratio between the in-channel power to the respective leaked side-channel power. Since in our specific architecture the side-channel power is mainly constituted by quantization noise, we will consider through this thesis the Adjacent Channel Power Ratio (ACPR), which is ratio between the in-channel power to the respective total side-channel power. We respectively

obtain 76.3 and 78.4dB. But this value can vary a little (<1dB), depending on the chosen channel. Here, we choose the 8th channel for this simulation.

On Figure 2-25, the SNDR is plotted versus the input level referred to the quantizer. It shows that the maximum stable input is $-3dB_{FS}$ and that the dynamic behavior of the modulators is in agreement with the expected one.



Figure 2-25 Simulated SNDR for the ideal configuration

2.3 Conclusion

We have presented here an architecture for achieving digital RF generation, thus enabling a digital radio. This architecture uses $\Delta\Sigma$ modulators to provide 1-bit high-speed data streams containing all channels information, owing to their oversampling and noise-shaping features. The $\Delta\Sigma$ modulator is the core of this system and its design is detailed in the next chapter. Essential surrounding blocks, that ensure proper RF signal generation and $\Delta\Sigma$ modulators functionality, have been described. Issues for the output power amplifier and antenna filters have also been handled. Besides $\Delta\Sigma$ modulators, key points of this architecture are the sample rate conversion block, which oversamples the signal for proper $\Delta\Sigma$ modulation, and the digital upconverter, that really creates the RF signal from the baseband oversampling $\Delta\Sigma$ -modulated digital signal. UMTS standard has been chosen in order to dimension the system blocks.

CHAPTER 3 DELTA-SIGMA MODULATOR SYSTEM DESIGN

This chapter will concentrate on the $\Delta\Sigma$ modulator system design. The previous chapter explained the role of this block inside the transmission chain, dealing with interconnections with surrounding blocks (sample rate conversion and digital upconversion). From there, the required architecture for $\Delta\Sigma$ modulators has been defined. In this chapter, physical implementation at high sample rate will be investigated, leading to the introduction of different design concepts:

- The system architecture will be optimized to be suitable for a high-speed digital implementation.
- The modulators' coefficients will be scaled down to powers of two.
- The use of a redundant arithmetic scheme will reduce the length of the critical path by enabling carry-free additions.
- Non-exact quantization of the output signal is used, because the carry propagation issue has been transferred to the output quantizer.
- A precomputation of the quantization output is needed to parallelize the output computations and reduce the critical path even more.
- Differential signals will be used everywhere inside the modulator core.
- Fast dynamic logic will be investigated.

The last two points will be detailed in the next chapter, dealing with circuit considerations.

3.1 $\Delta\Sigma$ architecture optimization

The $\Delta\Sigma$ architecture needs further optimization given the high clock frequency (3.9GHz for UMTS). The principal obstacles are the multipliers implementing the coefficients in front of the adders. The architecture has been simplified by replacing all coefficients by their closest power of two. This leads to the coefficient of Table 3-1. Multiplications simply become right shifts (for negative powers of two) and can be implemented with little effort in the routing scheme. No extra gates are then required to implement these operations.

Coeffi- cient	Value	Implemented value	Coeffi- cient	Value	Implemented value
a ₁	0.1409457518558072	2-3	c ₁	0.3166424812531309	2-2
a ₂	0.2435218988625833	2-2	c ₂	0.1684863887945898	2-3
a ₃	0.0945693329735421	2-3	g 1	0.0219599951361829	2-5
b ₁	0.1409457518558072	2-3			

Table 3-1 Power-of-two coefficients for the $\Delta\Sigma$ modulator



Figure 3-1 Third-order $\Delta\Sigma$ modulator architecture

Moreover, in the designed modulator of Figure 3-1, the accumulator, which is a zerodelay integrator, would increase the longest path, thus limiting the maximum reachable clock frequency. This path goes from the output of the third 1/z block, through g_1 feedback and several adders, to the input of the same block. To reduce this path, the accumulator has been changed into an integrator, according to the architecture in Figure 3-2 and simulated to evaluate the degradation.


Figure 3-2 Optimized $\Delta\Sigma$ architecture. The accumulator has been replaced by an integrator.

Simulated performance obtained with this new architecture is not so much degraded, considering the complexity reduction. Spectrally, the zeros are slightly shifted but they remain close to the band limits. SNDR versus amplitude level is plotted on Figure 3-3. Maximum SNDR is slightly reduced by about 3dB. Concerning ACLR for 5 and 10MHz offsets, the simulation show maximum values of 74.7 and 72.2dB, respectively, for the maximum input signal amplitude.



Figure 3-3 SNDR comparison for ideal and simplified architecture

In a digital implementation, signals are quantized, which is not taken into consideration within the Matlab model. By contrast, VHDL simulations offer the possibility to quantize the amplitude of processed signals. A VHDL model of the architecture has been

simulated with different number of bits for input and internal nodes. Table 3-2 shows the SNDR degradation for several cases. Amplitude quantization brings degradation in the system dynamic performances. An input signal of 16 bits is chosen. The input $2^{-3} b_1$ coefficient can be omitted, leading to a 13 bits input signal. These values will be the reference for further optimizations.

	Matlab	VHDL 28bits	VHDL 24bits	VHDL 16bits
SNDR	72.16dB	71.7dB	71.47dB	70.61dB

Table 3-2 SNDR degradation for Matlab and VHDL simulations

To conclude, the reduced complexity for the $\Delta\Sigma$ modulator design justifies the very light degradation in dynamic performances. The complexity reduction consisted in scaling the coefficients to the nearest power of two, suppressing the zero-delay integrator and quantifying internal signals.

3.2 Logic design issues

3.2.1 Critical path and digital implementation issues



Figure 3-4 $\Delta\Sigma$ modulator architecture showing data registers

From the defined architecture, presented on Figure 3-2, we can go deeper to highlight the digital implementation. All integrators will be computed as registers with output signal added to the input signal. Then the architecture can be computed as the one on Figure 3-4. Registers have been displayed prominently and coefficients, which are implemented with no propagation delay and have no effect on timing analysis, are displayed on signal paths.



Figure 3-5 Critical path

Timing analysis of this architecture highlights the critical path, constituted by the fourinput adder placed in front of the input of the second register. This critical path is detailed in Figure 3-5. The quantizer provides a 1 bit output, so it works as an evaluation of the sign of the input signal. In classical 2's complement representation (C2), the sign is explicitly handled by the Most Significant Bit (MSB). Thus, this quantizer does not introduce any additional propagation delay.

Finally, critical path is essentially composed by adders, as in every other paths. The most critical one comprises four 16-bit signals to add (or subtract). As it consists of a direct-path signal and three feedback signals, the best optimization would be to compute the signals two-by-two in parallel, leading to two consecutive 16-bit additions as shown on Figure 3-6. It also makes the circuit insensitive to glitches, as the signal paths are matched.



Figure 3-6 Architecures for 4-inputs additions

Registers in the $\Delta\Sigma$ modulator are clocked at a 3.9GS/s rate. That means the period between two clock edges is 1/3.9GS/s = 256.4 ps. For easier explanation in following discussions, a 250ps period will be considered. This statement leads us to find a 16-bit adder structure able to operate faster than a half clock period, i.e., 125ps. One can note that this assumes ideal registers (no propagation delay and no setup time), which is surely not the case, as it will be discussed later.

Pipelined structures could help in relaxing constraints related to the high sampling rate. Unfortunately, due to the feedbacks and the associated coefficients, no pipelining of this architecture is conceivable.

3.2.2 Adder architectures analysis

In this section we will review adder implementations at the block and circuit level. An extensive coverage of this topic can be found in reference [28]. In a first part, possible architectures for adding digital signals will be detailed. Then, the focus will be put on circuit design. Analysis of logic gates for adder implementation will be covered and propagation time in deep submicron CMOS technologies will be highlighted through simulations results.

The simplest known adder architecture is the Ripple Carry Adder (RCA) presented on Figure 3-7 for a 4-bit implementation. A *N*-bit adder is constructed by cascading *N* full-adder (FA) circuits. The sum *S* and carry *C* output signals are described by the following Boolean equations:



Figure 3-7 4-bit Ripple Carry Adder architecture

The carry propagates across the N stages, thus the worst-case delay occurs when a carry generated at the Least Significant Bit (LSB) position must propagate to the Most Significant Bit (MSB). The corresponding delay for a N-bit adder is equal to

$$t_{RCA} \approx (N-1)t_{carry} + t_{sum},$$
 Eq. 3-2

where t_{carry} and t_{sum} are the propagation delays from C_n to C_{n+1} and S_n , respectively. This structure has a propagation delay proportional to the word length. Many other structures can help in reducing the dependency of propagation delay on the word length [46]. The characteristics of the most popular structures are summarized in Table 3-3.

The Manchester Carry Chain (MCC) adder makes use of the well-known generate g_n , propagate p_n and kill k_n functions defined as:

$$g_n = a_n \oplus b_n, \ p_n = a_n \cdot b_n \text{ and } k_n = \overline{a_n} \cdot \overline{b_n}$$
 Eq. 3-3

This structure does not reduce the worst-case propagation delay (when the carry always propagates), but speeds up other cases. An implementation example can be found in [47].

Carry SeLect (CSL) adder have a \sqrt{n} propagation delay behavior. Two additions are performed in parallel; one assuming the input carry is zero and the other assuming the input carry is one. The decision is made when the carry is finally computed. An implementation example can be found in [48].

Finally, the Carry LookAhead (CLA) adder is a powerful implementation due to its $\log n$ behavior. More circuitry is needed to estimate the carry for higher weight stages, but it greatly speeds up the processing. It is the most widespread implementation for high-speed adders [49].

Adder type	Abbreviation	Time	Area
Ripple Carry Adder	RCA	O (<i>n</i>)	O (<i>n</i>)
Manchester Carry Chain adder	MCC	O (<i>n</i>)	O (<i>n</i>)
Carry SKip adder	CSK	$O(\sqrt{n})$	O (<i>n</i>)
Carry SeLect adder	CSL	$O(\sqrt{n})$	O (<i>n</i>)
Carry LookAhead adder	CLA	$O(\log n)$	$O(n \log n)$
Signed-Digit Adder (base-r)	SD-r	${ m O}(b)^{*}$	O (<i>n</i>)
Borrow and Carry-Save Adder	CSA	O(1)	O (<i>n</i>)

b is the number of bits per digit

Table 3-3 Time and Area requirements for most popular *n*-bits adders

Most of these architectures use two's complement number system. Other number representations, like Signed-Digit or Borrow-Save, lead to powerful adder implementations with propagation delay independent of the word length.

3.2.3 Circuit level adders design considerations

This section evaluates adder structures at the circuit level in order to identify implementation issues and justify the architecture choice. The present study of full-adder propagation delays structures has been made in STMicroelectronics 90nm CMOS technology.

The carry evaluation is the worst critical operation with respect to the global adder speed. In a standard full-adder, carry evaluation needs three AND gates in parallel, followed by a 3-input OR gate, as shown on the left of Figure 3-8. One way to implement the full-adder circuit is to take its logic equations and translate them directly into static complementary CMOS circuitry. Standard cell gates from the 90nm design kit are described in a databook [50]. The corresponding transistor diagram of a full-adder is depicted on the right hand side of Figure 3-8. The calculated propagation delay for a 1-bit full-adder carry evaluation would be about 85ps for this logic style and 100ps for sum evaluation. It is clearly not possible to reach the required total delay of less than 125ps for a 16-bit adder.



Figure 3-8 Carry combinational logic and STMicroelectronics 90nm design kit static logic implementation

Several pass-transistor logic families for macrocell design have been proposed to improve performances of static CMOS circuits [48]. Complementary pass-transistor logic (CPL) is one example. An even more competitive implementation is the double pass-transistor logic (DPL), which is a modified version of CPL that resolves noise margins and speed degradation when designed for low supply voltage circuits.



Figure 3-9 DPL gates and full-adder implementation [48]

Figure 3-9 shows gates implementation and full-adder design with DPL logic from [48]. One can notice that all signals are complementary, thus this logic style doubles the number of pass-transistors with respect to CPL. Moreover, it is a non-restoring logic and so additional inverters are required. Simulations of the full adder in STMicroelectronics 90nm CMOS process have been performed. Globally, the propagation delay for sum evaluation is about 40ps and about 35ps for carry evaluation, with no output load. High-speed designs are enabled with this static logic style.

Finally, dynamic logic yields high switching speeds due to low load capacitance and small area thanks to the small number of transistors. Hold circuitry is included and no additional registers are needed. However, it is harder to implement and needs clock generation and distribution blocks, which will consume additional power. Also issues such as charge sharing, charge leakage or clock feedthrough, appear.

Due to the high switching speed requirement, dynamic logic will be the logic style chosen for the prototype circuit implementation. Dynamic logic will be explained in detail in the next chapter, dealing with circuit design. As a conclusion, achieving very high-speed digital processing is not an easy task. Efforts have to be made on adder architecture design as well as on transistor circuit design.

3.3 ΔΣ architecture with redundant arithmetic

3.3.1 Redundant number representation

The major limitation of arithmetic using natural binary or 2's complement representation is the word length dependant propagation delay. Alternative number representations can overcome this limitation at the cost of extra hardware. Carry-save and signed-digit representations belong to redundant representations. The Borrow-Save (BS) representation, also known as Binary Signed-Digit (BSD) or radix-2 Signed-Digit, is part of the signed-digit one and will be detailed hereafter.

If a two's complement number representation is $A = a_{n-1} \dots a_1 a_0$ then a_{n-1} denotes the sign of the number. The magnitude of A is given by

$$A = -a_{n-1} \cdot 2^{n-1} + \sum_{i=0}^{n-2} a_i \cdot 2^i$$
 Eq. 3-4

An unsigned carry-Save number representation is made up of 2 digits for each bit weight, each of which consists of a sum and carry pair (ac_{n+1}, as_n) , where $ac_{n+1}, as_n \in \{0,1\}$ and $as_n = ac_0 = 0$, *n* being the word length. This number is noted

$$A = \begin{cases} ac_{n}ac_{n-1}...ac_{1} \\ as_{n-1}...as_{1}as_{0} \end{cases}$$
 Eq. 3-5

Its value is given by

$$A = \sum_{i=0}^{n} (ac_i + as_i) \cdot 2^i$$
 Eq. 3-6

Binary Signed-Digit is somewhat similar to carry-save, by the fact that each bit weight is coded by two digits. The BSD coded number representation is $A = a_{n-1}...a_1a_0$ but now the $a_i \in \{-1,0,1\}$ and it can be stated $a_i = (a_i^+, a_i^-) = a_i^+ - a_i^-$. The magnitude is

$$A = \sum_{i=0}^{n-1} a_i . 2^i$$
 Eq. 3-7

Thus, the couples of digits (0,0) and (1,1) represent the value 0. In the same manner, (1,0) and (0,1) respectively codes for 1 and -1. Figure 3-10 illustrates the differences between two's complement, carry-save and borrow-save for 8-bit numbers and introduces a dot

notation that will be used in this thesis [51]. Full dots will stand for a positive bit (posibit) and empty dots stand for a negative bit (negabit). Full dots can take the values 0 or 1, empty dot the values 0 or -1.



Figure 3-10 Dot notation of two's complement, Carry-Save and Borrow-Save representation

3.3.2 Structures for redundant addition

Borrow-Save (BS) arithmetic enables carry-free addition, which means that there is no carry propagation anymore when this coding scheme is used [52]. Let's take an example to illustrate this property. Coding scheme for two's complement and Borrow-Save will first be depicted. Then, two's complement addition will be reminded. Finally, logic cells for redundant additions will be introduced and BS addition will be explained.

Let '5' and '-4' be two numbers to be added. The decimal result is '1'. If two's complement representation is chosen, '5' and '-4' are coded 0101 and 1100, respectively. On the other hand, in Borrow-Save, '5' and '-4' could have several representations, hence it is called redundant. '5' can be coded, for example, $\begin{cases} +0101 \\ -0000 \end{cases}$, $\begin{cases} +0101 \\ -0010 \end{cases}$ or $\begin{cases} +1000 \\ -0011 \end{cases}$, while '-4'

can be coded $\begin{cases} +0000\\ -0100 \end{cases}$, $\begin{cases} +1001\\ -1101 \end{cases}$ or $\begin{cases} +0011\\ -0111 \end{cases}$.

The successive steps in a two's complement representation are illustrated in Figure 3-11. For these 4-bit numbers, 4 calculation steps are needed, each requiring one FA (full-adder) cell.



Figure 3-11 Addition in two's complement

For Borrow-Save arithmetic, modified FA cells, called signed-FA cells, are used. They are similar to a FA but with one input and the sum output inverted, as shown in Figure 3-12a and Figure 3-12c [53]. Thus, with a signed-FA, either two posibits and a negabit or two negabits and a posibit can be added. The result will be a negabit (resp. posibit) of the same weight and a posibit (resp. negabit) of higher weight (Figure 3-12b). As FA cells can be called "+++" or "---", signed-FA cells are called "++-" (FAPPM) or "--+" (FAMMP), derived from the input polarities.



Figure 3-12 (a) "++-"-type signed-FA cell; (b) dot notation for "++-" FAPPM and "--+" FAMMP types and (c) logic table related to the signed-FA cell

Using the dot notation introduced earlier, the process of a BS addition is depicted on Figure 3-13. For adding two BS numbers, the steps are relatively simple. Two BS numbers will be represented by two couples of posibit/negabit for each weight. Using FAPPM cells, three dots can be computed at a time. Thus, the first step consists in translating three dots of each weight into a dot of the same weight and another of higher weight. The remaining intermediate line of dots is simply copied to the next stage. Next step is computed with FAMMP cells, leading to a reduction of the BS inputs into one BS output. One can note that, as all computations are done in parallel, two computation steps are required regardless of the input bit width.

Let us now consider the addition of '5' and '-4'. Figure 3-14 illustrates three examples of this addition, according to different possible BS representations of the numbers '5' and '-4'.



Figure 3-13 Addition process of two BS numbers. Little dots are free places.

5	+0101	+ 0 1 1 1	+ 1000
	-0000	- 0 0 1 0	- 0011
+ -4	+0000	+ 1001	+ 0 0 1 1
	-0100	- 1101	- 0 1 1 1
1	- 0101	- 1100	- 1000
	+0101	+1101	+1000
	- 0100	- 1101	- 0111
	+ 0 1 0 1 - 0 1 0 0 1 = 1	+ 1 1 0 1 - 1 1 0 0 1 = 1	+ 1 1 1 1 1 - 1 1 1 1 - 1 1 1 0 1 = 1

Figure 3-14 Addition in BS notation

Any number representation system can be used for the addition, provided it is represented in dot notation. For example, an easy computation is the addition of a BS number and a C2 number in order to provide a BS number Figure 3-15. This addition uses a single stage of FAPPM connected in parallel to provide the result. However, the MSB cannot be computed with a simple FAMMP, because the resulting notation would not fit the BS notation. A special-FA cell, described in Figure 3-16, has to be designed for this operation.

The inputs are two negabits and a posibit, and it provides a negative sum S and two carries (a negative *NC* and a positive *PC*). The corresponding equations are also given in Figure 3-16.



Figure 3-15 Addition process of a BS number and a 2's complement number



Figure 3-16 Special-FA cell equations, dot notation and logic diagram

In conclusion, all combinations of inputs can be computed. The addition boils down to reduce input bits to a BS coded number, using FAMMP, FAPPM, FA and special-FA cells. The number of steps needed for an addition strictly depends on the number of input signals to be added. In [54], Dadda's method is introduced to efficiently compute the sum of several inputs. Let's introduce the following sequence, defining the number of steps, given the number of input signals to add (BS signals count for 2 signals, whereas C2 signals only count for one):

$$u_o = 2, u_1 = 3, u_2 = 4, u_3 = 6, u_4 = 9, u_5 = 13, \dots, u_{j+1} = \lfloor 3u_j / 2 \rfloor$$
 Eq. 3-8

.

The subscript numbers denote the number of steps, while the values of the sequence indicate the number if input signals. This confirms that for adding two BS numbers (considered as 4 inputs), two steps are needed. However, for 3 input signals (a BS and a C2, for example), a single step is required. Table 3-4 illustrates this method.

Number of input signals	Number of steps	
2	0 (no computation)	
3	1	
4	2	
6	3	
9	4	
13	5	

Table 3-4 Illustration of Dadda's method

3.3.3 ΔΣ modulator architecture in BS representation

This section deals with the application of BS arithmetic inside the third-order $\Delta\Sigma$ modulator described in a previous part. An example of application of redundant representation in $\Delta\Sigma$ modulators can be found in [55]. The $\Delta\Sigma$ modulator architecture is recalled in Figure 3-17. It has been reorganized to combine adders and registers into a single block (dynamic logic). Signals in BS notation are drawn in bold lines Bit widths for each signal have been determined from simulations of the architecture with typical input signals.



Figure 3-17 Third-order $\Delta\Sigma$ modulator architecture

It is recalled that 2^{-n} blocks are simply right shift operations, when digitally implemented in 2's complement notation, and do not require any computational effort. However, with BS notation, if the signal is shifted and truncated, then there might be an error equal to one LSB. We will see later that those errors do not cause significant performance degradation. All stages will be detailed hereafter with the dot notation introduced earlier.

The first stage is presented in Figure 3-18a. It is composed of two blocks: the first one subtracts the 13-bit input with the sign *Y* multiplied by 2^{12} . The second one adds a BS number with a C2 coded number. This operation has been described in the introduction and is depicted in Figure 3-18b. The B1 block shown on Figure 3-19 is a special case. Although it should be possible to use a classical C2 adder for this operation, a more attractive solution is proposed. One can observe that if *Y* is equal to 1, then the result of the subtraction will be negative whereas if *Y* is equal to 0, the result would be positive. More generally, let us take an input signal coded on *N*-bits.

When *Y*=0, -2^{*g*} (i.e. "1...10...0") must be subtracted, thus "0...010...0" must be added.

When $Y=1, 2^{g}$ (i.e. "0...01...1") must be subtracted, thus "1...10...01" must be added.

So, in both cases, " $\underbrace{Y...Y}_{R-g-1}$ 10...0Y " has to be added.

In the present case, R - g - 1 = 3, which defines the architecture for the B1 block. The LSB addition has been deleted to avoid any carry propagation. The error introduced should not be relevant. However, it can be corrected by inserting *Y* into the B2 block output signal, because the positive LSB of the result is left empty. Finally, the B1 block of Figure 3-19 is composed by a simple inverter.



Figure 3-18 (a) Details of the first stage and (b) dot notation associated with the B2 block



Figure 3-19 Details of the B1 block

The second stage is the most complicated one as it computes three BS signals and a sum signal. This operation can be performed with three stages of signed-FA, as shown in Figure 3-20. Y signal is considered, like in the first stage, as "*Y*10...0*Y*".



Figure 3-20 (a) Details of the second stage and (b) dot notation associated with B3,B4 and B5 computation blocks



Figure 3-21 (a) Details of the third stage and (b) dot notation associated with B6,B7 and B8 computation blocks

Figure 3-21 describes the third stage. The input is composed two BS numbers plus the *Y* feedback signal, thus two steps are required for the addition. The last step computes the result of B7 block with the *Y* input to provide the 16-bit output BS signal. Identically to previous stages, *Y* is noted "*YYY*10...0*Y*". A special-FA cell is used for the MSB computation of the last block.

3.3.4 Simulation results

Concerning the BS-implemented $\Delta\Sigma$ modulators, Figure 3-22 shows an evaluation of the ACLR performances for both C2 and BS implementation. The input signal is the 8th WCDMA channel. Performance of the BS architecture is almost identical to the C2 implementation, and even slightly better. The simulated ACLRs are 76.2 and 73.7dB, respectively, for 5 and 10MHz offsets.

To study integrators saturation, several types of inputs have been tested. The Full-Scale (FS) is defined as the maximum amplitude at the quantizer. For example, for a signed 16 bits input, FS is [-32768; 32768]. This modulator can accept:

• Any DC level included between -21000 and +19000, i.e. 61% of FS. This is acceptable, because DC levels at the modulator input are rarely high and commonly near zero.

- A sine wave up to an amplitude of 22000, i.e. 67% of FS. This result is justified by the characteristic of the $\Delta\Sigma$ modulator, which saturates at -3dB_{FS}.
- Any WCDMA channel between -27.5MHz and +27.5MHz up to the maximum amplitude. The maximum amplitude is defined by the peak value of the pattern. Thus, a backoff equal to the peak-to-average ratio of the modulated signal is needed.



Figure 3-22 ACLR performance comparison on the ΔΣ modulator output signal spectrum for 2's complement (blue) and Borrow-Save (red) architectures

3.4 Output quantizer in Borrow-Save arithmetic

3.4.1 Non-exact quantization

The BS architecture has been defined in order to remove any carry propagation, which enables very high-speed digital processing. The output quantizer evaluates the sign of the output. In two's complement representation, the sign is obviously given by the MSB polarity. However, with BS notation, sign evaluation is not an easy task, because all bits affect the sign. Thus, a carry must be propagated all along the 16 quantizer input bits. A logic comparison between the positive and the negative input bits must be performed.

Unfortunately, the critical path, determined earlier, contains the output quantizer. Therefore, any excessive propagation delay on this block must be avoided, as all the benefits brought by the BS notation is lost in this operation.

The solution is inspired by the analog implementation of $\Delta\Sigma$ modulators. Dithering is sometimes performed before quantization to avoid signal harmonics raise and to wreathe the shaped noise [41]. Concretely, some kind of noise is added to the signal before quantization. It is shown that this added noise does not degrade the performances as it is also shaped away from the band of interest. Looking at this, the idea of performing a non-exact quantization comes to the fore.

The number of bits used in the logic comparison has been progressively reduced and $\Delta\Sigma$ modulator performances have been evaluated. This has led to a drastic reduction in the comparison complexity. In fact, a 3-MSB comparator is able to achieve similar performances than a 16-bit comparator, as shown on the plot of Figure 3-23. (a) and (b) dot notations in Figure 3-24 depict the progressive reduction of the number of bits considered in the comparison.

To go further, a logic study of the output bits values has shown that the positive and negative MSBs are always equal for all non-saturated input signals listed above, and that the negative 15th bit is always null. This is depicted on the (c) dot notation. Thus, they do not affect the output sign and can be left unused. Finally, with our architecture, the sign can be easily computed with the equation presented on Figure 3-24.



Figure 3-23 Evaluation of the $\Delta\Sigma$ modulator performances with nonexact quantization



Figure 3-24 (a), (b) and (c): Dot notations related to the bits considered inside the logic comparator

Performance evaluation has been made in the same conditions as before, leading to the plot of Figure 3-25. It relates a slight increase in the in-band noise for the non-exact quantization. There is a trade-off to make between the comparator complexity and the performances obtained. Table 3-5 sums up the ACLR values obtained with the respective architectures. For BS implementation with non-exact quantization, the ACLR falls down by

about 6dB to about 68dB. For remembering, ACLR limits defined by the UMTS norm allows -33 and -43dB for 5 and 10MHz offsets, respectively. These simulation results let a reasonable margin for disturbances introduced by output stages.

	ACLR @ 5MHz	ACLR @ 10 MHz
Two's complement	-74,7 dB	-72,2 dB
Borrow-Save with exact quantization	-76,2 dB	-73,7 dB
Borrow-Save with 3-bit non-exact quantization	-68,8dB	-67,4 dB

Table 3-5 ACLR comparison for different ΔΣ modulator architecture



Figure 3-25 ACLR performance comparison on the $\Delta\Sigma$ modulator output signal spectrum for BS architecture with exact (red) and non-exact (red) quantization

3.4.2 Output signal precomputation



Figure 3-26 Precomputation of the sign; *Y* is evaluated in parallel with the stage 3 output signal.

Although the output comparator complexity is greatly reduced, its computation needs available time to be correctly performed, which is not the case in the implementation explained in the previous parts. Parallelizing the comparator operation with the computation inside the third stage seems to be a good solution to physically implement the global function. This is what is called precomputation of the sign. It is depicted on Figure 3-26, with the sign evaluation in parallel with the B8 block.

Let's take the general case of Figure 3-21b in which two BS signals are added together with the C2-coded *Y* signal. If the comparison is made on the two MSBs, then the global logic operation to perform is $Y = Out_{+}^{16}\overline{Out_{-}^{16}} + Out_{+}^{15}\overline{Out_{-}^{15}}(Out_{+}^{16} + \overline{Out_{-}^{16}})$ to evaluate the sign of the signal. There are two possibilities to determine the sign of the BS signal, because zero can be assimilated either to a positive or to a negative number. Thus, either $Y = Out_{+}^{16}\overline{Out_{-}^{16}} + \overline{Out_{-}^{15}}(Out_{+}^{16} + \overline{Out_{-}^{16}})$ or $Y = Out_{+}^{16}\overline{Out_{-}^{16}} + Out_{+}^{15}(Out_{+}^{16} + \overline{Out_{-}^{16}})$ can be chosen. The first equation is more practical, as it uses Out_{-}^{15} , which is directly produces by a special-FA at the same time as Out_{+}^{16} and Out_{-}^{16} , from the A_{15} , B_{15} and Y bits, as denoted on Figure 3-21b. Combining this logic equation with the special-FA ones, one can demonstrate that $Y = A_{15}\overline{B_{15}} + A_{15}\overline{Y} + \overline{B_{15}}\overline{Y}$. This is the precomputed equation for 2-bit sign evaluation and can be easily computed as only three terms are used.

The same reasoning can be executed if a 3-bits comparison is pointed out. The initial logic equation is $Y = Out_{+}^{16}\overline{Out_{-}^{16}} + (Out_{+}^{15} + \overline{Out_{-}^{14}})\overline{Out_{-}^{15}}(Out_{+}^{16} + \overline{Out_{-}^{16}})$ and can be reduced to $Y = A_{15}\overline{B_{15}} + (A_{14} + \overline{B_{14}})(A_{15}\overline{Y} + \overline{B_{15}}\overline{Y})$, while considering the B8 block equations. Five terms are used here which leads to a more complicated precomputation.

Moreover, the comparator block could be placed in parallel with the B7 and B8 blocks, but, in most cases, the number of different terms to compute grows with the depth of precomputation. Thus, this solution has been aborted.

Finally, the global idea is to find the easiest equation (involving minimum terms) for precomputation, even sometimes by reorganizing addition structures inside the third stage.

3.5 Conclusion

The system design of the third-order $\Delta\Sigma$ modulators has been covered by this chapter.

First, the global architecture has been defined. Then, a logic description has stated the limitations in terms of high-speed implementation with a 3.9GS/s sample rate. Techniques for achieving this high sample rate have been developed.

- The use of redundant arithmetic inside the modulator enables carry-free additions. So the maximum length critical path is reduced to three full-adders.
- A dynamic logic transistor implementation will help in performing the additions. This aspect is process dependent, hence, for future CMOS technologies, dynamic logic can be replaced by easy-to-implement static logic using, for example, pass-transistor logic. The dynamic logic used in our architecture will be described in next chapter, which deals with transistor design.
- A non-exact quantizer is designed to reduce the borrow-save sign evaluation complexity, which needs carry propagation.

• An output sign precomputation parallelizes the non-exact quantization operation with the last computation stage, in order for the output signal to be available for the next sample period.

All these techniques (except dynamic logic) for achieving high-speed $\Delta\Sigma$ modulators are deeply covered by a co-authored patent [56] and a conference paper [57].

CHAPTER 4

DIGITAL TRANSMITTER CIRCUIT DESIGN

4.1 Transmitter IC description

4.1.1 IC structure



Figure 4-1 Processing blocks implemented inside the transmitter IC prototype

The designed transmitter IC comprises all processing blocks highlighted on Figure 4-1. The core is the delta-sigma modulators, associated with the digital quadrature upconverter. It also handles clock generation and distribution, pre-amplification and a part of the sample rate conversion block (the 16-time oversampling sub-block). For demonstration and control purposes, a few blocks are added, as shown on Figure 4-2. These ones are the Delay Locked Loop (DLL) block, the output registers and the control block. The DLL block provides finely controlled delayed clocks from a unique external master clock. Output registers are useful for testing purpose. They act as serial-to-parallel (S/P) converters. The control block provides all the useful signals for proper operating conditions.



Figure 4-2 IC block structure

For describing the whole transmitter circuit design, the outline will be as follow. The global structure and layout will be presented. Then, inside the following sections, we will detail the circuit design and the generated layout for each block separately: the sample rate converters, the delta-sigma modulators, the DLL block and the digital quadrature upconverter. Output registers will not be detailed as they are commonly implemented. The control block will not be investigated either, as signals of interest will be evoked inside main processing blocks description.

4.1.2 IC configuration and layout

The first prototype transmitter IC has been designed in STMicroelectronics 90nm CMOS process. The layout is shown on Figure 4-3. It sizes around $3 \times 1 \text{ mm}^2$ and counts 96 pads. Top (resp. bottom) side comprises the 13-bit I (resp. Q) input and half of the parallelized I (resp. Q) outputs. I and Q signals at the 3.9GS/s output of the $\Delta\Sigma$ modulators are paralelized into 243.75MS/s 16-bit streams. The choice has been made, for reducing the pin count, to output only the first 8-bit half or the second 8-bit half of this stream and a control

signal enables to choose which half to output. On left side is principally found the master clock input pad. The right side hosts the analog output pads. Control pads are dispersed all over the pad ring where room is left.



Figure 4-3 First prototype IC layout

The pad ring is supplied with 2.5V and the core is working under a 1 to 1.2V power supply. Core power supply is divided in 3 areas; one for the clock circuitry (VddCLK), another for digital processing blocks (VddDS) and the last one for analog output stages (VddANA). Thus, power consumption can be evaluated separately for each block. It is to note that proper pad ring functionality with 90nm process requires a compensation cell, which compensates for process and temperature variations.

4.2 Sample rate conversion block design

4.2.1 Block structure

To be recalled into mind, the sample rate conversion block implemented inside the prototype IC is simply a 16-time oversampler able to transform the 245.76MS/s (250MS/s

will be used in the sequel for more conciseness) input sample rate into the 3.9GS/s rate of the delta-sigma modulators. This operation is not difficult to implement as it is only composed by registers, as shown on Figure 4-4. In the clock scheme used, the IC provides the 250MHz main clock and the output stages of outside components (mainly FPGAs) are sampled with this clock. It avoids outside generation of synchronous clocks. However, other schemes could be used, which are synchronicity-independent. For example, for the second prototype IC, the clocking scheme has been modified. Clock is provided by the outside and resynchronized on the input. It is depicted on Figure 4-5. This data acquisition process will work whatever is the phase relationship between the clocks. We will see in the next chapter on test equipment that the second solution is more practical to implement.



Figure 4-4 Input sample rate conversion block and clock scheme



Figure 4-5 Clock scheme used for data acquisition in the second prototype IC

As described in a previous chapter, an operation of linear interpolation must be accomplished on Q channel to avoid images from rising above the quantization noise. Since the input signals are oversampled 16 times with a sample-and-hold function, the resulting operation, described in Figure 4-6, is relatively simple. The input symbol on Q channel is repeated 15 times, while the 16th one is calculated from two successive symbols. This can be implemented using the structure of Figure 4-7. The switch command is used to place the calculated 16th symbol at the right place. This switch command is easily generated from the 250MHz clock. Registers sampled at 4GS/s delays it and an appropriated logic gate combines the original clock with the delayed one and thus produces the switch command. It is to note that an equivalent delay is introduce on I channel for synchronicity.



Figure 4-6 Qualitative I and Q signals at the $\Delta\Sigma$ modulators input. Q signal has been linearly interpolated on each sample.





4.2.2 TSPCFF registers

For transistor implementation, D flip-flops able to work at few GHz must be designed. The edge symmetry is also a criterion of choice. In literature, the dynamic True Single Phase Clock Flip-Flop (TSPCFF) appears to be one of the fastest [28]. Moreover, as stated in its name, it uses a single phase clock, which is a valuable asset. The schematic and layout of this flip-flop is displayed on Figure 4-8. The layout sizes $5.4 \times 4.5 \,\mu\text{m}^2$.



Figure 4-8 Schematic and layout of the TSPCFF

Figure 4-9 describes the mechanism of operation. When the clock signal is low, *D2* node is stuck at Vcc through the conducting PMOS. This phase is called "precharge". Thus, *out1* node is left high impedance and *out* node is its complementary. These latter nodes keep their preceding values ("hold" phase). *D1* node is the complementary of *D* input.

When the clock signal goes high, then D2 becomes dependent over the D1 value. This is called "evaluation". If D1 is low, then D2 does not change its precharge value. If D1 is high, then D2 node is discharging through the NMOS transistors. The nodes *out1* and *out* follow the D2 node as they are in an inverter configuration ("active" mode).

The registering operation is very fast, but output edges rise and fall times and related propagation delays could be very different. First, output NMOS and PMOS are sized in order to equalize rise and fall times. Let's detail the reasons why propagation delays could be different to find an acceptable solution.

In the case of a rising output edge, the hold value of out1 is 1. When made active with the rising edge of the clock and D2 evaluated as 1 (not discharge), then the time for out to become 1 is the time to discharge out1 and charge the out node.

In the case of a falling output edge, the hold value of out1 is 0. When made active with the rising edge of the clock, D2 is evaluated as 0. This node must discharge before out1 and out gets their values. Thus, the time for out to become 0 is now equal to the time taking to discharge D2, charge out1 and then discharge of out node.

An acceptable solution for equalizing the propagation delays for each transition is equating the *out1* discharge time with the *D2* discharge plus *out1* charge times, by adjusting sizes of N and P MOS transistors. In fact, *out1* discharge must be slowed down whereas its

charge must be fastened. This can be made by simulating the flip-flop to find the best optimization. An eye-diagram for an 8GHz clock, presented on Figure 4-10, describes the performance of the optimized flip-flop. The output rise and fall times are varying from 17 to 22ps depending of the process corners (fast or slow). The propagation delay is equal to 40ps for the best implementation case.



Figure 4-9 Mechanism inside the TSPCFF when clock signal is low (left) and high (right)



Figure 4-10 Eye diagram of the TSPCFF output signal for a typical process corner and a temperature of 80°C

4.3 Digital delta-sigma modulator circuit design

4.3.1 Global structure





The third-order $\Delta\Sigma$ modulator architecture is drawn on Figure 4-11. As described on Figure 3-18, Figure 3-20 and Figure 3-21, each stage comprises, at the most, three logic layers, each built up from signed-FAs, signed-HAs or buffers. From this statement, the idea is to design a brick-like architecture. As the gate switching speed is the main parameter for our application, the previous chapter has stated dynamic logic was the logic style of choice. Using differential dynamic logic does not require any register anymore because the storage function is implicitly implemented. However, each dynamic logic layer requires its own clock to be functional. Thus, for three logic layers, three clocks would be used, each delayed from the others by a third of the period. Figure 4-12 depicts the layout of the dynamic logic base bricks. A DLL (explained later) will be useful to generate multiphase clocks.

Each differential dynamic logic layer will be evaluating the gate output into a third of a period. During the unused time, the dynamic gates will precharge themselves to be ready when their respective clocks will rise up.



Figure 4-12 Layout of the basic bricks and relationship between the three different clocks

4.3.2 Dynamic FA circuit description



Figure 4-13 Differential dynamic FA cell circuit diagram (transistor gate lengths are minimal)

Details of a differential dynamic Full-Adder cell are presented on Figure 4-13. The principle of operation of such a cell is quite similar to the dynamic flip-flop cell presented

earlier. It counts two succeeding stages: a precharge/evaluation stage followed by a hold/active clocked inverter (tri-state inverter). When the clock is low, intermediate nodes are precharging to the high state through the PMOS transistors and the outputs are high impedance. At the moment the clock signal is turning to '1', outputs are made active and reflect the intermediate node evaluation. One intermediate node over the two stays high, whereas the other one is discharging itself into the conducting FA NMOS logic and the clocked NMOS. FA logic for sum and carry evaluation is not depicted here as it is simply a differential NMOS logic network.



Figure 4-14 Transient response of a FA cell with an ideal clock

A transient simulation of such a cell can be found on Figure 4-14. For this simulation, inputs of the FA cell are chosen to be a 3-bit counter; hence there are 8 states in the graph. The simulation is done with a 250ps ideal clock with 30ps rising and falling edges. We can observe, from top to bottom, the clock, the intermediate precharge node, the sum output, the differential intermediate precharge node and finally the differential sum output. Evaluation and precharge phases have been displayed prominently. During precharge, all intermediate nodes are precharged to 1 (up arrows), while the outputs are held (right arrows). During evaluation, the intermediate nodes are evaluated to the computed value. The output sums are inverted and then take their final value for the period.

The propagation delay of this gate is around 50ps in the worst case when loaded by an identical gate. Larger output loads and additional initialization circuitry, which will be discussed hereafter, will slightly increase this value. One can note that in any case the effective propagation delay is not defined by the circuit itself, but rather by the third of the applied clock period, assuming the circuit could operate at the desired rate.

For validation, the global transistor circuit has been simulated and bit-to-bit compared to system simulations. It does not show any discrepancies.

The global consumption of the whole $\Delta\Sigma$ modulator with its initialization circuit has been evaluated by simulations, as though it is not the critical point of this study, contrary to speed enhancement. It would consume around 20mW. A previous identical design with a 130nm process has shown a consumption of 36mW. We can hopefully think that a further technology shrink (65nm process) will still reduce this estimated consumption.

4.3.3 Initialization circuitry

A major drawback is that this system comprises feedbacks. In fact, if no care is taken, the two nodes of a differential signal could be equal when powering up the system. Then, as outputs are fed back on inputs, the non-differentiality of these signals keeps the circuit stable into this bad and non-operating state. So an initialization phase is fundamental.

Forcing outputs to be differential is a solution to ensure a good startup of the system. Thus, a reset signal is needed, coming from outside the chip or from the locked flag of the DLL. To implement this control, two transistors are added inside the block controlled by CLK3, as shown on Figure 4-15.

On this figure, clocked inverter symbols have replaced the previous transistor diagram for the sake of clarity. The added transistors are controlled by the complementary signal *-R*, active when high. It forces the *SUM* output to be low by pulling its level through a NMOS transistor. No conflict happens because *SUM* is either high impedance or logically stuck at '0' when in the reset state.

For the complementary output _*SUM*, the intermediate node is pulling down only when the clock signal is high, in order to avoid conflict when this node is precharging. For that purpose, the NMOS transistor width has been reduced. If not, a non-defined level between high and low state might appear during precharge.


Figure 4-15 Dynamic FA cell circuit diagram, including the reset circuitry

A potential problem now appears when the reset signal is relaxed (from '1' to '0'). Examine the case when the reset signal is released during of the evaluation period (clock is high) and that the expected evaluation result is SUM = 1 and $_SUM = 0$. The intermediate node for *SUM* will be discharged during the evaluation period and when the reset is relaxed, *SUM* output will stick at '1' (provided the reset signal left time for the level to rise). For the complementary intermediate node, the FA logic will not be conducting but the reset-controlled transistor will be, so this node will also discharge itself and could never rise again before the next period. That means *_SUM* output will stick at '1'. *SUM* and *_SUM* would not constitute a differential signal anymore. Errors will propagate to all nodes due to the $\Delta\Sigma$ feedback structure. To sum up, the reset signal must relax itself during a precharge period.

To perform this, the reset signal has to be synchronized with the clock signal, what is not easy to realize and would not operate for a wide range of frequencies.

In a perspective of configuration, another initialization circuitry has been developed. It is illustrated on Figure 4-16. The cross-coupled NMOS transistors have two purposes. The first one is to maintain a differential output signal whatever are the inputs. Only one side can discharge, as it automatically blocks the other side. Secondly, this structure acts as a latch, so it can operate at any frequency (of course limited by the worst case propagation delay). Unfortunately, the addition of this cross-coupled transistor slightly slows down the operation, compared with the above architecture.



Figure 4-16 Dynamic FA cell circuit diagram, with an improved reset circuitry (The FA logic has been split in two differential blocks)

4.3.4 ΔΣ modulator layout view

The layout of the $\Delta\Sigma$ modulators is rather dense, because of interconnections between the base blocks. A strategy for correctly connecting all these blocks must be adopted. STMicroelectronics CMOS 90nm technology offers 7 levels of routing metal (two uppers are thick metal levels). Figure 4-17 details the routing strategy and the different types of interconnections. The three sum stages are staggered and shifted according to the multiplicating power-of-two factors. Thus, direct connections from one block to the following are routed straight ahead in second and third metal levels (first level is kept for internal cell routing). The integrators feedbacks are integrated into each stage. Stage outputs are routing directly back into stage inputs on the third metal level. Then, the global feedback is routing over the second and third stages, using fourth metal level. Finally, the output sign is fed back to the requested inputs using fifth and sixth metal levels.

Clocks and reset signals are routed vertically in an upper metal with a ladder type routing and access points to the cell are spread all over the distance. Power supplies and grounds are not represented on this figure. They are horizontally comb-routed all over the $\Delta\Sigma$ modulator layout.



Figure 4-17 $\Delta\Sigma$ modulator layout routing strategy

One can observe on the left of Figure 4-18 the arrangement of the three stages and the network of interconnections. Power supplies and ground rails are not shown. A bit slice has been highlighted and zoomed in on the right of the figure. On it, one can observe the clock and reset distribution rails as well as the three logic cell inside each sum stage.

Details of the dynamic signed-FA cell layout are given underneath. Two parts compose this cell: a fixed part implementing the dynamic logic circuitry for precharge and evaluation and a configurable part, which lets one choose the desired logic function to realize (sum or carry in the case of a FA).



Figure 4-18 ΔΣ modulator layout

4.4 Clock generation and distribution

To make dynamic cells operating, three clocks, at 0°, 120° and 240° are needed [58]. They are produced with a Delay Locked Loop (DLL). Its principle of operation is illustrated on Figure 4-19 [59]. The main component is a controlled delay line in which delays are functions of an applied voltage. In this case, three identical delay elements deliver the desired clock signals. To be able to synchronize these clocks on a reference clock, the phase of the latter one is constantly compared with the phase of the last generated clock (CLK3). The phase detector will provide the phase information to a charge pump. From this information, the voltage applied to the delay line will be increased or decreased. Thus, CLK3 will be

dephased exactly by one period, whereas CLK1 and CLK2 will be respectively dephased by 120° and 240°.



Figure 4-19 Global structure of a DLL

The 3.9GHz reference clock is delivered from the 7.8GHz IC main clock. This clock is brought to the circuit via an external source and is internally divided to provide the 3.9GHz and 250MHz clocks. Then, the produced clocks are synchronized with rising edges of the 7.8GHz clock. Several clock domains exist in the whole IC: one for the $\Delta\Sigma$ core in which the clock tree has been designed carefully to equalize all the delays on clocks signals; another for the multiplexer and output stages and a last one for the S/P blocks. Clocks are synchronized locally inside each clock domain [60].

4.4.1 Controlled delay line description

The delay line is constituted by inverters with voltage-adjustable delays and static inverters, as shown on Figure 4-20a. The voltage-adjustable delays are controlled by Vn and Vp, provided by the charge pump. The role of the static inverters is to reshape the possibly degraded signal.

To implement delay elements, several solutions are conceivable. In one hand, a digital delay control can be implemented by adjusting the inverter load [61]. The load is traditionally constituted by capacitors or transistor gates banks, switched according to the control word. This type of control adjusts the gate propagation delay as well as rise and fall times. On the other hand, an analog control, like the one implemented here, is constituted by an inverter in

which a NMOS and a PMOS has been added in series in the main branch, as on Figure 4-20b [62]. The rise and fall times are better controlled than with the digital control. Only one NMOS or PMOS could be used, but it would unbalance the rise and fall times of the clock signals.



Figure 4-20 Inverter chain constituting the voltage-controlled delay line

4.4.2 Phase comparator and charge pump

The phase comparator provides information about the phase relationship between the reference clock and CLK3. Its principle of operation is described on Figure 4-21. In a first step, clock frequencies are divided by two in order for the succeeding computations not to be critical. The phase detector is waiting for a rising edge on each clock to reset its output (Figure 4-22). The RS flip-flop triggers on with the first rising edge and keeps holding its value until the second sets in. Its output signal is returning to zero when inputs are falling down. This flip-flop provides an *UP* signal, meaning the voltage *Vn* must be increased and a *DOWN* signal, meaning it must be decreased. The charge pump brings or removes a defined charge quantity from the storage capacitor. *Vn* is then obtained on the capacitor and *Vp* is created using a diode-mounted transistor in order to have Vp = Vdd - Vn (give or take the transistors threshold voltages). Adequate controlling voltages are obtained from this phase comparison.



Figure 4-21 Phase comparator and charge pump schematics



Figure 4-22 Phase comparator and charge pump signals

4.4.3 DLL mechanism and clock signals characteristics

The DLL has two operating phases: a calibration phase and a locking phase. In the initial state, delays are set to the minimum by sticking Vn to Vdd. During calibration, Vn

voltage is decreasing slowly and Vp increases similarly, until they stabilize when the clocks are locked in phase (Figure 4-23). Then, the charge pump is continuously adjusting the voltage around this locking state. In simulations with a 100µA current source for the charge pump, the calibration phase lasts between 50 and 100ns for a few GHz clock.



Figure 4-23 Evolution of Vn and Vp during calibration and locking phases



Figure 4-24 CLK1, CLK2, CLK3 and reference clock waveforms.

Figure 4-24 shows output signals of the DLL for a 4GHz clock (250ps period) when locked. The locking error between CLK3 and the reference clock is around 5 picoseconds. Simulated clock characteristics are summed up in Table 4-1. Duty cycles are near 50% and rise and fall times are acceptable.

	Duty cycle	Rise time	Fall time	Phase delay (+/ 5ps)
CLK1	51%	37ps	23ps	83ps (33%)
CLK2	51%	38ps	23ps	84ps (34%)
CLK3	52%	43ps	25ps	84ps (34%)

Table 4-1 DLL clocks characteristics for 4GHz clock reference. The load isconstituted by one ΔΣ modulator.

Consumption has been evaluated during simulations. It largely depends over the sizes of the chain delay transistors. For about 100µm width PMOS and 50µm width NMOS, the calculated consumption is around 50mA under 1.2V. We could expect this consumption to be greatly reduced going though next generation technology process. It is to note that for further configurable architectures, wide-range DLLs must be designed [63].

4.5 Digital mixer and output stages design

A previous section has described the digital mixer and output stages principle of operation and different types of non-idealities brought to the output signal of this stage. It has been stated that edges symmetry must be guaranteed by the use of a differential structure, as shown on Figure 4-25. In fact, all symbols must have the same energy. The digital mixer stage will be designed with great care for generating a signal with the most symmetric edges.



Figure 4-25 Differential output stages architecture

It must be considered that processing the signal into these stages correspond to a conversion from digital to analog [64]. Thus, the above structure must operate independently of the data and of the operating sample rate, in order to equalize the energy for each bit and to respect RF signal integrity.

4.5.1 Digital mixer structure

The study of the digital mixer structure is part of Axel Flament's thesis work and is fully detailed in his thesis report [65] and in an article [64]. Here are only given some elements for understanding.

The digital mixer relies on a multiplexing operation. It could be realized with D flipflops and transmission gates, as illustrated on Figure 4-26. The first transmission gates let us choose either I (resp. Q) or its complementary (resp. Q complementary). The second gates selects either I channel or Q channel. Three clocks and their complements have to be used with this architecture: one at 4 times the carrier frequency f_c (7.8GHz), another divided by two (3.9GHz) and the last one at f_c (1.95GHz). They are produced and synchronized locally, as they are only used there.



Figure 4-26 Multiplexer architecture

Critical paths for this architecture are presented in the left of Figure 4-27. The architecture must ensure that data going through the last flip-flop have traveled the same path length and established themselves with the same accuracy. This is to keep the delay data-independent, which is not obvious to realize with high-frequency switching.

Highlighted critical paths have different lengths due to the opposite phase clocks controlling the transmission gates. To synchronize critical paths, a TSPCFF is inserted on Q channel and clocks phase controlling transmission gates are inverted. The computed function stays identical, but now time to reach the input of the last flip-flop is rigorously identical for I and Q channel. Delays has become independent over data and working frequency.



Figure 4-27 Multiplexer architecture, showing (left) critical paths and (right) the adopted solution for data-independent signal paths

4.5.2 Output stages

Output stages following the digital mixer are acting both as a pre-amplifier and as a 1bit digital-to-analog converter. They are simply a chain of growing inverters, able to drive a 50Ω load under a 1V power supply. Inverters had to be sized in order to guarantee the output signal edge symmetry. A simulated eye-diagram is shown on the left of Figure 4-28 to outline obtained performances at the differential output of the buffers for an 80°C temperature and a slow process corner. We show a zero-crossing differential signal with 23ps rise and fall times. Modeling pads and bonding wires to come closer to a realistic simulation leads to the eyediagram on the right of Figure 4-28. It depicts rising and falling times twice than simulations without pads and bonding wires models.



Figure 4-28 Eye diagrams for 50Ω-loaded buffers differential output signals for a slow process corner at 80°C (a) without and (b) with an electrical model for pads and bonding wires

4.6 Conclusion

A first 96-pad $3 \times 1 \text{ mm}^2$ prototype IC has been developed in STMicroelectronics CMOS 90nm technology. Circuit diagrams and layout for the main parts of the prototype IC have been explained in full details into this chapter:

- The sample rate conversion blocks, including the interpolation circuit on Q channel, has been detailed. A focus has been made on the design of high-speed dynamic flip-flops, known as True Single Phase Clock Flip-Flops (TSPCFF)
- The digital $\Delta\Sigma$ modulators have been fully covered, with a top-bottom approach and emphasizing on initialization circuits and layout arrangement.
- The Delay-Locked-Loop multiphase clock generation block has helped in dealing with dynamic logic inside the $\Delta\Sigma$ core by providing three dephased clock signals.
- Finally, the digital mixer, digitally implemented by a multiplexing operation and output buffering stages has been reviewed.

Inside those circuit descriptions, other architectures have been propounded. They will be used in a second prototype, detailed in next chapter. This second prototype will enhance the first version and correct some unsuccessful choices.

Implementation of dynamic gates requires a clock generation block, initialization circuits and a complex layout. But, at the moment, if this circuit wants to be demonstrated, then the switching speed is the priority. In a near future, design complexity would be reduced by using high-speed static logic gates, like DPL logic style. Consumption would also be greatly reduced, by removing DLL blocks, which consume a lot.

CHAPTER 5 EXPERIMENTAL RESULTS

5.1 First prototype IC (FULBERT I)

5.1.1 Test hardware description

5.1.1.1 Measurement tools

The first prototype IC has been described in the previous chapter and its structure and layout was presented on Figure 4-2 and Figure 4-3, respectively.

The scheduled measurements are the analysis of the analog output spectrum and the recovery of the output digital data stream. These two test protocols are depicted on Figure 5-1 and Figure 5-2, respectively. A sine wave generator provides the 7.8GHz main clock to the device under test (DUT). This clock is centered on 0.5V with a DC bias tee. The differential outputs are directly connected to a spectrum analyzer through DC blocks.

Data from I and Q channels are sampled at 250MS/s. As we do not possess or have access to an arbitrary waveform or pattern generator, which can handle this sample rate, a less powerful arbitrary waveform generator (AWG420 [66]) is used to produce a digital 16-bit wide word at 125MS/s. FPGAs are implemented and programmed to upsample the incoming signal and filter out images. The signal is brought to the DUT through an impedance-controlled connector (MICTOR). Another FPGA is used to make an interface to the logic analyzer, decreasing the sample rate of the output digital stream. It is to note that the test must be done twice, because only half of the output stream is output during each run. A marker is generated at the beginning of each test run to be able to recall the good sequence. For clock management, the clock scheme is the following: the DUT provides a 250MHz clock to the FPGAs. The latter ones generate a synchronous 125MHz clock and control the measurement instruments. The two 125MHz clocks could have a different polarity, depending on which

edge of the 250MHz clocks is counted up first into the FPGAs, leading to synchronization issues. Another clock scheme strategy will be adopted in the second prototype.



Figure 5-1 Test hardware for the analog output analysis



Figure 5-2 Test hardware for the digital output test **5.1.1.2** Test boards and assembly

Several printed boards are designed to realize this test. First, as ICs are delivered naked, a substrate must be designed. ICs will then be wire bonded onto the substrate. The

substrate will then be soldered onto a daughter board, on which are placed all the circuits for control, analog I/Os and power supplies. Finally, the daughter board is placed on a motherboard through high-speed impedance-controlled MICTOR connectors. The motherboard hosts the FPGAs, programming interface, memories and all the connectors for connecting instruments.

The substrate is a FR4, 4-layer, $24 \times 12 \text{ mm}^2$ printed circuit board (PCB) with state-ofthe-art constraints on track width and isolation. Tracks on which the IC will be bonded are $50\mu\text{m}$ wide and spaced by $50\mu\text{m}$ from other tracks. As the IC pad pitch is $80\mu\text{m}$ and the PCB pitch is $100\mu\text{m}$, angles at extremities are around 40° , which is in fact too high for a reliable and repeatable wire bonding operation. Figure 5-3 shows a picture of the substrate on which an IC has been wire bonded at the center. Figure 5-4 shows the daughter board and the motherboard.



Figure 5-3 IC wire bonded on the substrate, soldered on the daughter board



Figure 5-4 Daughter board (left) and motherboard (right)

5.1.2 Measurement results

5.1.2.1 Issues

When measurements were executed, a main issue had appeared. Huge oscillations on power and ground inside the chip have been observed, when the sample rate was increased. In fact, not enough decoupling capacitance was present on-chip, as the only decoupling was lying inside some pad ring cells. Moreover, the core power supply is divided in three parts: clock, $\Delta\Sigma$ core and output stages. There were not so many power supply pads for each separated supply. As the circuit is wirebonded and huge current peaks (especially on clocks and output stages) flow into the wires, voltage potential differences are created according to the well know inductance equation:

$$U = L \frac{dI}{dt}$$
 Eq. 5-1

This effect has been post-simulated to confirm the problem. Bonding wire inductance, ground-related capacitance and resistance have been evaluated according to its shape and fitted with an electrical model. This model shows that bonding wires introduce around 1nH of inductance.

With this values and assuming an ideal off-chip power supply, transient simulations have been performed. The simulation concentrates on on-chip supplies and clock signals as shown on Figure 5-5. The clock goes through the vddCLK domain, then through vddDS domain. Unfortunately, the vddCLK supply shows large variations (around 500mVpk) when the chip is enabled, due to high current peaks in this clock domain. vddDS only slightly varies

(<100mV). Figure 5-6 shows effects of supply variations on signals. Clock signals hardly suffer from the vddCLK variations, especially during the phases when the voltage is decreased. It behaves as the gates operation is frozen by the low voltage supply. Thus, when the clk7g8 signal is going through the vddDS domain (not affected by that disturbance) then the resulting clock does not look like a clock anymore. The high-speed functionality of the IC is deeply affected by this effect and could not be demonstrated.









For lower operating frequencies, the circuit does not suffer from those huge variations. Unfortunately, the $\Delta\Sigma$ core could not be initialized properly, because the reset circuit presented on Figure 4-15 is not working for a wide range of frequencies. It has been designed for working with a 7.8GHz main clock. At low frequencies, the $\Delta\Sigma$ outputs are not differential as they would be.

So, supplies variations prevent the high-speed operation, while low frequency operation is not authorized by the initialization stages. A second prototype, detailed in next subpart, has been designed to correct these two points.

5.1.2.2 Output stages measurements

The only achievable measurement on this circuit is an evaluation of the output stages, when the circuit is on reset state. The $\Delta\Sigma$ outputs are then stable and differential. Thus, the output sequence is $[I,Q,\overline{I},\overline{Q}] = [0,0,1,1]$. In that case, the output is a periodic signal with a frequency equal to the main clock frequency divided by 4. An eye diagram has been drawn on Figure 5-7, although the signal is not randomly distributed, in order to figure out the output signal shape for a 3.9GHz input clock (half the desired operating frequency).



Figure 5-7 Eye diagram of the IC output for a 3.9GHz input clock. The IC has been placed in its reset state

A measurement concerning output stage consumption has also been realized. The output stage consumption (comprising digital mixer and output buffers) has been noted down for different frequencies. The circuit has been put in its reset state and the supply voltage was 0.95V. The obtained result is presented on Figure 5-8. The useful current flowing through the

 50Ω load is approximately equal to 18mA. The output stages current consumption increases with the frequency with a slope of about 8mA/GHz. Thus, we can extrapolate to the desired frequency of 7.8GHz. Switching losses will reach about 60mA, which results in a maximum efficiency of 25% (the efficiency is here defined as the load current to the total current ratio).



Figure 5-8 Current consumption in output stages

5.2 Second prototype IC (FULBERT II)

5.2.1 Changes and enhancements



Figure 5-9 Layout of the second prototype IC



Figure 5-10 Die microphotograph of the prototype chip in 90nm CMOS

Test of the first prototype IC has revealed crucial points to be redesigned in order for the circuit to be functional. Changes and enhancements have been brought to a second prototype IC in STMicroelectronics 90nm CMOS. As the circuit is a redesign, its structure is similar to the first prototype. Layout of this circuit is presented on Figure 5-9 and die microphotograph on Figure 5-10. Here are the main changes from the first attempt:

- The circuit is now sizing $4 \times 0.8 \text{ mm}^2$ and counts 103 pads.
- Assembly has been restrictive for the first prototype, because chosen dimensions were at the PCB technology limits. The signal pad pitch has been enlarged to 150µm, according to the easier and cheaper PCB fabrication. Moreover, ground pads have been intercalated between each signal pads. For the assembly, a large ground plane is placed under the IC and all grounds are wirebonded on it. Signals are wirebonded a little further to 75µm-wide tracks. With that kind of assembly the ground would be almost perfect inside the chip.
- All power supplies inside the circuit have been connected together. This unique power supply will be equal to 1 or 1.2V. We lost the possibility to evaluate the power consumption of each block separately but, as power pads are disseminated all over the map, the bonding wires global inductance will be decreased. It should be better for making a reliable power supply.
- Digital outputs have been suppressed to gain room.
- On-chip decoupling capacitors have been added to avoid variations over supply voltages. The total added capacitance is around 800pF.
- The $\Delta\Sigma$ core initialization stage has been redesigned to be able to operate properly at any frequency (according to the schematic of Figure 4-16).
- Clock scheme used inside the digital input blocks has been modified. The clock is now provided by the instrument tools (refer to Figure 4-5).

5.2.2 Test hardware description



Figure 5-11 Test setup for the second prototype IC

The test setup is almost similar to the first prototype IC apart from the digital output stream acquisition that has been dropped out. An arbitrary Waveform Generator (AWG420) will be loaded with a Matlab file containing the WCDMA baseband signal. A FPGA will oversample and filter the complex signal, before applying it to the DUT, in the same time as the data clock. Main clock will be provided to the Device Under Test (DUT) by a frequency synthesizer through a bias tee. Generators will be synchronized and calibrated by using an external 10MHz reference synthesizer. Finally, RF outputs will be visualized on a spectrum analyzer centered on the band of interest (or on a digitizing oscilloscope or a modulation analyzer, depending on the measurement to be performed).

The chip has a differential RF output but most instruments inputs are single-end. A balun has been implemented between the chip and the instrument input interface. The chosen balun is a Mini-Circuits TC1-1-13M [67], which can operate until 3GHz. At this rate, the average insertion loss is around 3dB.

On Figure 5-12 is shown a photography of the test boards and chip assembly. The chip has been wire-bonded on a little FR4 substrate and has been protected by black resin for shipping. Decoupling capacitors are present on the board as close as possible to the chip. Then the substrate has been soldered on the main board, which shelter components useful for power supply and control signals handling and connectors for digital input signals. These signals are coming from two FPGA boards containing an Altera Cyclone II. The master input

clock comes from the SMA connector at the bottom of the picture and the two SMA connectors at the top are for the differential RF outputs.



Figure 5-12 Photography of the chip assembly and test boards

5.2.3 Measurement results

Globally, the chip shows full functionality up to a 4GHz main clock frequency. The targeted clock frequency is 7.8GHz but the core seems not to be functional at this desired rate. Therefore, the maximum achievable center frequency is 1GHz. However, the first image band, situated at ³/₄ of the main clock frequency can be used, thus reaching a 3GHz carrier frequency. The counterpart of this is that the signal is attenuated by the sin_c shaping function and that the bandwidth is limited to 50MHz (half the designed one). The measurement results achieve most standards requirements, on the fundamental frequency, as well as on the image band. When moving the main clock frequency, every parameter, defined for a 7.8GHz main clock functionality, is proportionally reduced. For example, the UMTS standard can be addressed with a 2.6GHz main clock frequency, so the image band falls around 1.95GHz.

To relate the measurement results, we will first demonstrate the digital core functionality. Then we will focus on a single clock frequency, which is 2.6GHz, to measure the dynamic performances. We will finally study the evolution of the main parameters with the frequency.

5.2.3.1 Core functionality



Figure 5-13 Digital and analog spectrum measurements for a 2.5GHz main clock and a DC input signal

To show the right functionality of the digital core, we use an Agilent Infiniium series digitizing oscilloscope. As it can have a sampling frequency of 5GS/s, the main clock has been set to 2.5GHz in order to have 2 samples by symbols. Hence, we could acquire a frame on which an FFT can be performed. Doing this leads to a frequency spectrum of the analog output signal. The digital output stream can be retrieved by determining if each sample is a digital '1' or '0'. Then the analog disturbances (such as jitter, supply voltage variations, etc...) are suppressed, leading to a frequency spectrum of the digital data output stream. These two frequency spectra are plotted on Figure 5-13 for a DC input signal.

The digital data stream spectrum shows the desired $\Delta\Sigma$ noise shaping. The in-band mean noise is -146.5dBm/Hz. The estimated SNDR is 72.15dB over a 30MHZ bandwidth. The analog output spectrum shows a higher in-band noise floor. Measurements on the analog signal will be detailed inside next sections.

5.2.3.2 Measurement results at a 2.6GHz main clock frequency

All measurement results with a 2.6GHz clock will be presented hereafter and a summary will be given in the last part.

Frequency Spectra

The modulated input signal is a WCDMA QPSK signal at a 3.84MHz symbol rate sampled at 81.25MS/s (2.6GHz / 32). It is filtered by a root raised cosine filter with a 0.22 roll-off factor, so the spread signal occupies a 5MHz wide channel. This signal has a Peak-to-Average Power Ratio (PAPR) of 8.1dB. This means the mean power of the signal is 8.1dB lower than a sine wave with the same peak power. For the following plots, the peak power has been set to $-3dB_{FS}$, the full-scale being the quantizer scale.

The first test setup includes generation of the signal with the baseband processing chain presented in this report. Measures with this signal do not provide optimum results. Excessive noise is present inside the bandwidth. For rapid and accurate generation, the Tektronix MCIQ utility has been used to generate the IQ desired signal. This tool lets us obtain good measurement results but we have lost the possibility to choose the channel placement. The generated channel is inherently in the middle of the band. Investigations on the signal generation method are still ongoing in order to find the critical block and to resolve the problem.



Figure 5-14 Wideband spectrum of the chip output at 650MHz with a 5MHz input channel with a span of 200MHz (a) and 500MHz (b). RBW is the resolution bandwidth.

Frequency spectra have been acquired with an Advantest R3265 spectrum analyzer. Figure 5-14a and b depict wideband spectrum of the 650MHz band with, respectively, a 200MHz and a 500MHz span. The noise shaping of the $\Delta\Sigma$ modulators can be shown, as well as the flat in-band noise. One can observe a skewness between each side of the rising quantization noise. It is mainly due to the balun used on the differential outputs. Similar plots on the image band at 1.95GHz are depicted on Figure 5-15. Axes have kept the same ranges for easy comparison with the previous case. On these plots, two disturbances appear at about 21MHz around the carrier. It is brought by a coupling phenomenon, outside the chip, between the digital modules of the Arbitrary Waveform Generator and the clock interface. When the chip is running, it is hard to totally delete this, but it can be reduced by carefully positioning the test modules related to each others. On the 650MHz plot, this phenomenon is hidden by the quantization noise.



Figure 5-15 Wideband spectrum at 1.95GHz. The parameters are the same as Figure 5-14.

Figure 5-16 shows in-band spectra for 5MHz channels at maximum power, for the fundamental and the image band. The plot is centered on the channel of interest and the adjacent and alternate channels are shown on each side. From this, an Adjacent Channel Power Ratio (ACPR) can be measured. It is the ratio of the in-band power to the power of the adjacent (or alternate) channel. It can be read directly on the Y axis, by evaluating the difference between the two flat levels for the considered channels. In the left plot, the ACPR is around 52dB, while on the right plot, it is around 44dB. The difference stays in two points. First, the image is attenuated by the $\sin_c(f/f_s)$ shaping function. At $\frac{3}{4}$ of the sampling frequency, the attenuation is theoretically equal to 10.45dB. The signal is affected by this degradation, but not the noise, which is not correlated to the signal. The noise floor is only 3.2dB lower. This leads to around 8dB of total degradation on the ACPR value between the fundamental channel and its image.

The measured in-band power is respectively -3.9dBm and -15.8dBm. The in-band power has been measured on the 50 Ω load of an Agilent E8408A VXI Modulation Analyzer with the balun placed between the chip RF output and the load. Measured values have not been corrected with balun insertion losses.

Figure 5-17 depicts the measured output channel power related to the input channel power referred to the quantizer scale. It shows that for this kind of signal, $0dB_{FS}$ corresponds with an output channel power of -1.8dBm, integrated over 5MHz. It also shows that the output power is linear with the input signal amplitude and that there is a constant difference between the channel power in the fundamental band and in the image band. This difference is

around 11.7dB. It is slightly more than the predicted sin_c attenuation and is due to the balun higher insertion loss at higher frequencies.



Figure 5-16 In-band spectrum measurements for a 5MHz WCDMA channel for the fundamental (a) and the image band (b).



Figure 5-17 Output channel power versus the input channel power referred to the quantizer full-scale.

ACPR vs Channel Power

The ACPR has been studied according to the channel power with the same signal as described in the preceding paragraph, with an 8.1dB PAPR. The signal peak power is

considered for the full-scale reference. The ACPR is plotted on Figure 5-18 for the 650MHz and 1.95GHz bands. The maximum ACPR is 53.6dB and 44.3dB, respectively. These measured values meet the UMTS requirements (33/43dB for adjacent and alternate channels) even in the 1.95GHz attenuated image band.



Figure 5-18 ACPR vs Channel Power for adjacent and alternate channels around fundamental and image bands.

SNDR vs Channel Power



Figure 5-19 650MHz fundamental band : (a) Signal and in-band noise power on 30MHz related to the input channel power (b) SNDR on 30MHz vs input power.

For Signal-to-Noise and Distortion Ratio (SNDR) study, the input is a 5MHz sine wave. The amplitude of this sine wave is referred to the quantizer full-scale. OdB_{FS} refers to the peak power of the maximum coded sine wave.

The SNDR is plotted on Figure 5-19b. The peak value is 53.6dB over a 30Mz bandwidth for an input power of $-4.4dB_{FS}$. In system simulations, the SNDR peak value appeared for a $-3dB_{FS}$ input sine wave. Measurements show that the delta-sigma modulators saturate for an input sine wave power higher than $-4.4dB_{FS}$. On Figure 5-19a, the peak output power is 1.09dBm in a single-ended configuration and is obtained for $-3dB_{FS}$, although the SNDR is already degraded. For a differential output, the peak output power is 3dB higher, thus reaching 3.1dBm. For input channel powers lower than $-4.4dB_{FS}$, the noise floor is equal to -129.5dBm/Hz. For higher values, the in-band noise begins to rise, thus prematurely degrading the SNDR value.



Figure 5-20 1.95GHz image band : (a) Signal and in-band noise power on 30MHz related to the input channel power (b) SNDR on 30MHz vs input power.

Figure 5-20 shows the same plots for the 1.95GHz image band. The peak SNDR is 40.8dB over a 30MHz bandwidth for a $-4.4dB_{FS}$ input power. The peak output power is -8.59dBm into a differential load and for an input power of $-2dB_{FS}$. It is to note that the noise floor is equal to -129.4dBm/HZ and is almost the same as in the fundamental band (what was not the case when the ACPR has been studied). Furthermore, one can observe a different slope for low and high input powers in the SNDR plot, as well as in the signal power plot. These particularities, degrading the image band SNDR and system linearity, have not been explained yet and need further investigations.

EVM measurements

Error Vector Magnitude (EVM) has been measured with the Agilent Modulation Analyzer. Constellations have been acquired and the EVM for the 3.84MS/s RRC filtered QPSK downconverted signal is measured to 1.24% for the 650MHz band and 3.42% for the 1.95GHz band (Figure 5-21). For comparison, in UMTS, the EVM specification is 17.5% for output powers higher than -20dBm. Typical performance of analog transmitters is 7 to 8%.

A study of the EVM parameter has been made related to the channel power. Results are presented on Figure 5-22. For the 650MHz band, the EVM stays under 2% down to $-10dB_{FS}$. The EVM for the image band is higher and stays around 6%. For input powers lower than $-20dB_{FS}$, the EVM could not have been measured due to the sensitivity of the input stages of the instrument, which cannot handle such low signals. Further measurements must

be made with an amplifier before the instrument input stage in order to check if the EVM stays low or really increases. For high input powers, the EVM degrades due to the saturation of the $\Delta\Sigma$ core system.



Figure 5-21 IQ constellations for the fundamental (right) and image band (left). This plot leads to the EVM measurement.



Figure 5-22 EVM versus the input channel power

Output Jitter

Output jitter has been measured to investigate the degradation of the analog output spectrum measurement, compared with the digital data stream analysis presented before. The

2.6GS/s output signal has been applied to an Agilent Infiniium DSO 81204A oscilloscope to characterize it. The eye diagram of this signal is plotted on Figure 5-23. It shows a mean jitter of 13.24ps_{RMS}, an eye width of about 300ps (for a 385ps period) and an eye height of 636mV. According to non-idealities simulations presented in a previous section, we can conclude that the main contribution to the observed analog in-band noise is the output signal jitter. It has two possible sources. First, it comes from the phase noise on the main clock, which travels all along the chip and is surely disturbed by surrounded active switching area. Next, the supply voltage varies on the output stages, what can affect the switching threshold of the inverters and thus the switching instant. One more time, an emphasis is made on the cleanliness of the design of output stages and clock blocks.



Figure 5-23 Eye diagram of the 2.6GS/s output

Summary of measurements with a 2.6GHz main clock

Above measurements have been summarized in Table 5-1. The power consumption has been measured for the whole chip, due to the single 1V power supply. The relative contributions of the output stages and the core have been evaluated during first prototype measurements, where the output buffers consumption has been evaluated separately.

		2.6GHz clock		
		650MHz channel	1.95GHz channel (image)	
ACPR (5MHz	wide channel)	53.6dB	44.3dB	
Max Chanr	nel Power	-3.9dBm	-15.8dBm	
EV	М	1.24%	3.42%	
Output	jitter	13.2ps _{RMS}		
SNDR (BW	= 30MHz)	53.6dB	40.3dB	
In-band no	oise floor	-129.5dBm/Hz	-129.4dBm/Hz	
Peak output	ut power	3.1dBm	-8.59dBm	
_	total	69mW (1V)		
Power consumption	output stages	39mW		
	core	$2 \times 15 \mathrm{mW}$		

 Table 5-1 Summary of measurements with a 2.6GHz clock

5.2.3.3 Measurements at other frequencies

Each parameter measured previously for the 2.6GHz main clock frequency will be studied here for clock frequencies from 200MHz to 4GHz, thus addressing bands from 50MHz to 1GHz (from 1GHz to 3GHz for the image band) with a proportional bandwidth. The input power is fixed for these measurements and we can assume that the power behavior will be similar for all frequencies.

Power consumption

The power provided to the 50 Ω resistive loads is equal to 20mW under a 1V supply voltage. In fact, the two differential outputs deliver a 1V delta-sigma signal, whose average voltage is 0.5V. It leads to 10mA of current consumption into the 50 Ω load and consequently to a global power consumption of 20mW for the two differential outputs.

Power consumption has been plotted on Figure 5-24 for each clock frequency between 100MHz and 4GHz when the circuit is in its active state. This supply voltage has to be adjusted, so that the chip is operating properly and is shown in this figure for each frequency. The power consumption has been measured and then scaled to a 1V supply voltage reference for comparison and tendency analysis. It shows that the switching losses increase with the frequency with a nearly 20mW/GHz slope.



Figure 5-24 Chip total power consumption as a function of the clock frequency

Evolution of ACPR



Figure 5-25 ACPR versus carrier frequencies for fundamental bands

The ACPR has been measured for different working frequencies with a $-3dB_{FS}$ channel. Considering the fundamental bands, Figure 5-25 shows the ACPR for alternate and adjacent channels as a function of the carrier frequency. The channel width is proportional to

the carrier frequency and equals to 3.84MHz for the 650MHz center carrier frequency. The measured ACPR stays higher than 50dB for every frequency, except for the 1GHz carrier frequency. The UMTS requirements for ACPR are 33 and 43dB for adjacent and alternate channels. These specifications are fully completed.

Figure 5-26 shows a similar plot with the ACPR measurement extended to the image band. As explained before, the ACPR is attenuated by about 8dB for image bands. The measured values are around 43dB from 1GHz to 3GHz. They are at the limit of the 43dB requirement for alternate channels, sometimes a little worse. The measured difference for particular frequencies could be explained by a very sensitive device to every parameters of the test setup (supply voltage, clock frequency and DC bias and even perturbations brought by the digital inputs).



Figure 5-26 ACPR versus carrier frequencies for fundamental and image bands

Evolution of SNDR



Figure 5-27 Measured SNDR for different main clock frequencies

The SNDR has been measured with a sine wave at a few MHz (its frequency is proportional to the clock frequency) and with a $-6dB_{FS}$ power. It is plotted in Figure 5-27. The SNDR is calculated by measuring the ratio of the signal power to the noise power inside a bandwidth relative to the sampling frequency. It shows an almost constant SNDR value, except for two measurement points (at 1.4 and 4GHz) on which the noise level was particularly high when measured. The high noise floor for the 4GHz clock frequency (1GHz carrier frequency) could explain the degraded ACPR measured at this frequency in the preceding section. Measurement errors could be responsible for the isolated measured value at 1.4GHz.
Evolution of EVM



Figure 5-28 Measured EVM as a function of the main clock frequency

The Error Vector Magnitude is plotted on Figure 5-28 as a function of the main clock frequency. It has been measured for the fundamental bands with a frequency-relative bandwidth QPSK modulated channel at a $-3dB_{FS}$ peak power. From 200MHz to 4GHz, the EVM stays under 6%, most of the time around 2%. It degrades itself at particular frequencies around 1GHz, probably due to measurement incertitude. At clock frequencies near 4GHz, the EVM also increases, thus reflecting the previous observations.

Evolution of the channel power



Figure 5-29 Output channel power versus the main clock frequency

The channel power has been acquired and measured with the Agilent Modulation Analyzer. This output channel power is not constant with the frequency. It varies by about 4dB, depending upon the working frequency, as shown on Figure 5-29. The maximum output power is around -2dBm. Around a 1.2GHz and a 3GHz clock frequency, the output channel power degrades to -5.5dBm. These variations are hard to explain. The inserted balun could influence the channel power by amplitude and phase mismatch and insertion losses. A characterization of the implemented balun must be performed in order to define if the balun is really responsible for these variations or if other aspects interfere.

Evolution of the jitter



Figure 5-30 Data and clock jitter versus the main clock frequency

The output jitter is responsible for a huge part of the degradation on the output signal in-band spectrum. This analog behavior has been measured by acquiring the output data stream on an Agilent Infiniium oscilloscope. Figure 5-30 plots the measured values for different frequencies. First, the jitter has been measured when the circuit is in active state with input data. The data jitter increases with the clock frequency. It goes from $6ps_{RMS}$ at 1GHz to almost 15ps_{RMS} at 3.5GHz. When the circuit is in the reset state, outputting a periodical signal at a fourth of the clock frequency, the jitter is, for every frequency, around $2ps_{RMS}$. This demonstrates that the output data jitter does not come from the clock path. It rather comes either from the disturbances of the digital core switching activity on the clock signal or from the data-dependent behavior of the mixer and output stages.

Summary of measurements

Performances described for the 2.6GHz clock frequency remains relatively constant for other frequencies operation, up to 4GHz. ACPR measurements show values above 50dB for fundamental bands and around 43dB for image bands. It fulfils UMTS ACPR requirements for most frequencies. SNDR stays around 50dB, although the chip performances degrade for a 4GHz clock frequency. EVM stays under 6% for all frequencies when measured

with the maximum channel power. The whole chip power consumption is of course increasing with the frequency with a 20mW/GHz slope.

However, channel power and jitter varies with the frequency. More investigations are needed to explain the channel power variations. The jitter increases with the frequency, which is not surprising, due to the interactions between the digital core and the clock signals.

5.2.4 Comparison with similar works

	This work		[10]
Max Clock Frequency	4GHz clock		700MHz clock
Max Carrier Frequency	1GHz channel	3GHz channel (image)	175MHz channel
Max Adjacent ACPR (5MHz wide channel)	55dB @ 500MHz clock	44.5dB @ 2.4GHz clock	50.26dB
Max Alternate ACPR (5MHz wide channel)	57.2dB @ 500MHz clock	47dB @ 2.4GHz clock	40.27dB
Total Power Consumption	25mW (1V) @ 700MHz clock 69mW (1V) @ 2.6GHz clock		139mW (1.5V)
Total Silicon Area	3.2mm ²		5.2mm ²
Process	90nm CMOS (GP)		130nm CMOS

Table 5-2 Comparison with similar works

The only similar work has been reported in 2004 [10], but for IF frequencies. The clock frequency was 700MHz for a 175MHz IF carrier frequency. The ACPR measured for a 5MHz WCDMA channel are 50.26dB and 40.27dB, respectively for adjacent and alternate channels. In their system, the $\Delta\Sigma$ modulators bandwidth is pretty much the same as the channel bandwidth, what explains the bad value for alternate channel ACPR. The quantization noise is already increasing due to the limited bandwidth. It employs a current output and the full-scale current is 11.5mA. The die area of the chip is 5.2mm² and it consumes 139mW with a 1.5V supply.

Our work offers a higher working frequency, a larger bandwidth, a better ACPR for the fundamental band, a lower power consumption and a smaller die area, as compared in Table 5-2.

5.3 Conclusion

Two 90nm CMOS chips has been designed and fabricated from a STMicroelectronics process for demonstrating the digital transmitter proposed concept based on $\Delta\Sigma$ modulation. The first chip was not functional but brings valuable information for a redesign. The second chip has shown functionality up to a 4GHz main clock frequency, thus addressing a 1GHz maximum carrier frequency (or 3GHz if the image band is considered). Measured performances fulfill requirements for most standards, such as UMTS. Performances in the image band are a little lower, due to the inherent sin_c attenuation.

For a 2.6GHz clock frequency, the measured ACPR is around 53dB for a 5MHz wide channel and the channel output power is -3.9dBm. The SNDR is about 53dB over a 30 MHz bandwidth. The EVM is lower than 2%. The chip consumes 69mW on a 1V supply voltage and occupies a 3.2mm² die are (0.15mm² for the active area).

Those parameters remain almost constant for working frequencies from 200MHz to 4GHz.

The designed chip settles the state-of-the-art in $\Delta\Sigma$ -based digital RF signal generation in terms of working frequency. The measurement results obtained on this prototype are high enough for this kind of digital chip to replace existing analog implementations in a near future.

CONCLUSION

For the field of mobile communications, a digital RF transmitter using $\Delta\Sigma$ modulation has been demonstrated. A prototype 90nm CMOS chip has been designed, which fulfils requirements for standards such as UMTS. One of the potential advantages of a 1-bit coded digital RF signal is the ability to use class-S switched power amplifiers having a very high efficiency.

Parallel works

The architecture demonstrated here is the first reported transmitter chain using 1-bit digital $\Delta\Sigma$.modulation working in the RF domain

Previously, as evoked in the state-of-the-art and measurement results, the nearest implementation was made by Sommarek et al. [10] in 2004 for IF frequencies. The main clock frequency is 700MHz and the obtained ACPR is 50.26/40.27dB for adjacent and alternate channels. Our work marks a great advance in this field by moving the IF conversion to RF frequencies.

Several works on transmitters from other research teams have been performed during the three years of this thesis work. Two of those are of great interest [68, 69]. They explore a different way by proposing a Digital-to-RF Conversion (DRFC). A multi-bit D-to-A converter is merged with the mixer into the DRFC block.

In [68], 10-bit 307.2MS/s signals are applied to the DRFC. A 41/56dB ACPR is obtained for WCDMA 5MHz channels and an output power of 25dBm. The EVM stays below 2% over 60dB of control range.

In [69], a $\Delta\Sigma$ modulator is used to reduce the number of bits required in the DRFC to 3 bits. The $\Delta\Sigma$ modulator uses a second-order MASH structure and operates with a 2.5GS/s sample rate. The MASH structure has been chosen for its simplicity and relatively short critical path, only composed by a 12-bit adder. A passgate style adder with a differential sense-amplifier flip-flop scheme has been designed. The aiming standard is mainly the ~500MHz bandwidth WLAN around 5GHz. The proposed concepts and the chip design are very valuable and depict very good results. For comparison with our work, this implementation only works with very simple $\Delta\Sigma$ modulator structures and is not compatible

with more complex structures, such as the 3rd-order zeros-optimized architecture used in this thesis.

The DRFC structure is of great interest. However, one disadvantage of the DRFC structure is that it requires on-chip matching. Moreover, this structure operates inherently in current-mode, limiting at low voltage the maximum power that can be delivered to a load. In particular, class-S amplification is incompatible with a current-mode output.

Reconfigurability

The proposed architecture opens a way for easy reconfigurability and flexibility. The topology chosen for the $\Delta\Sigma$ modulators achieves a low and flat noise floor inside a band equal to the clock frequency divided by 80. The possible configurabilities in this prototype are to change the clock frequency value and the baseband signals to transmit. The frequency planning has to be carefully investigated. Thus, every standard, up to a 3GHz center frequency, can be addressed with the fundamental or image band, keeping in mind that the image band offers worse performances.

For optimum reconfigurability, coefficients of the $\Delta\Sigma$ modulator should be dynamically modified in order to place poles and zeros in a location appropriated to the aiming standard. Investigations on coefficient reconfiguration have not been yet engaged but should be stated as an objective for such an architecture.

We have recently begun to work on the possible location of zeros of the $\Delta\Sigma$ noise transfer function [70]. We have imagined to increase the order of the $\Delta\Sigma$ modulators and to place the added zeros in the band in which the noise constraints are the hardest to reach for any given standard. Doing this would greatly relax the filter requirements. A method for automatically placing poles and zeros for high-order $\Delta\Sigma$ modulators has been developed. An example, shown in Figure C - 1, has been taken for a UMTS/DCS1800 reconfiguration.

The UMTS configuration clearly shows 3NTF zeros in the UMTS TX band (one of them at the center band frequency and the two others near the band extremity). A zero has been placed in the DCS TX band and another in the UMTS RX band. The zeros are symmetrical around the carrier frequency. For the DCS1800 configuration, the clock frequency has changed and 6 $\Delta\Sigma$ modulator coefficients are modified. It leads to the placement of a zero on the DCS RX band (the other one is not in any specific band).



Figure C - 1 Output spectrum of a digital transmitter implemented with a configurable 5th order ΔΣ modulator in (a) UMTS configuration and (b) DCS1800 configuration

Future directions

The chip developed in this thesis work is at a prototype state. Many enhancements must be done in order to be able to replace advantageously the components in place and to integrate it into a complete transmitter.

First of all, techniques for achieving very high-speed computations inside the $\Delta\Sigma$ modulators have demonstrated a possible implementation with a 90nm CMOS process. Going further with smaller and faster process will surely open a way to reduce the core complexity. For example, investigations in 65nm have shown that, at transistor level design, the dynamic logic could be replaced by simpler DPL static adders. For the same kind of application, the latter logic style is, with a given technology, slower than dynamic logic style but is sufficient when implemented with faster transistors. This modification heavily reduces complexity, as the DLL 3-phase clock generation block becomes useless and the clock tree simpler.

Next, the filtering capability of such a digital RF stream, with huge out-of-band quantization noise, remained to be proven. BAW filters are a good candidate to such an application [32]. They are recently investigated inside the MOBILIS IST European project [71]. The goal of the MOBILIS project is to enable digital multi-band handsets by developing digital transmitter modules, combining a SoC digital integrated circuit (IC) with BAW filter and SiP RF power module along with a power amplifier and BAW filter/duplexer. Main challenges are the power handling capability and duration of BAW filters as well as the impedance matching between switching-mode DACs and BAW filters.

Other ways of output filtering must be investigated. An interesting way is developed in Axel Flament's thesis [65]. Power combining is performed with transmission lines to replace traditional power amplification stages. As it is a digital implementation, the proposed structure enables a FIR filtering capability, which could greatly relax the constraints on antenna filtering stages. This structure is in adequacy with a $\Delta\Sigma$ -based RF signal generator, as it takes advantage of the high efficiency of switching power amplification.

All-digital transmitters with $\Delta\Sigma$ modulation are serious candidates to replace wireless terminals analog front-end blocks. They offer reconfigurability, flexibility, robustness, reduced power consumption, better efficiency and better integration. But many bottlenecks still need to be overcome...

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Résumé en français

Le domaine d'application de ce travail concerne les communications mobiles et plus particulièrement les architectures de transmission. Ce travail de recherche introduit une architecture de transmetteur numérique qui permettrait de remplacer avantageusement les solutions matérielles actuelles. Cette architecture tire profit de la modulation $\Delta\Sigma$ d'un signal suréchantillonné qui permet de quantifier un mot numérique sur 1 bit sans toutefois perdre l'information utile dans le bruit de quantification apporté. La très haute cadence de cette partie numérique met en avant des limitations qui sont surmontées par des techniques innovantes. Un circuit prototype en 90nm CMOS a été développé pour démontrer le concept proposé.

L'organisation des parties est la suivante. Dans une première partie, la notion de radio logicielle est abordée. Un état de l'art sur les architectures d'émission est effectué pour replacer l'architecture proposée dans son contexte. Enfin, les principales spécifications du standard UMTS sont données. Ce standard sera pris comme exemple, dans un premier temps, pour la conception du circuit. La deuxième partie décrit l'architecture du transmetteur numérique proposé, en axant sur les choix architecturaux. La troisième partie est centrée sur le modulateur $\Delta\Sigma$ et décrit toutes les techniques utilisées afin de pouvoir faire fonctionner ce système numérique à cadence rapide. Le quatrième chapitre décrit la conception du transmetteur au niveau transistor. Chaque bloc est décrit en mettant en avant le schéma et le layout utilisé. Le dernier chapitre est consacré aux mesures sur les circuits prototypes. Les composants de tests et les résultats de mesures sont détaillés et comparés avec la littérature.

Ce résumé en français détaille, de façon concise et rapide le contenu de chaque chapitre en anglais, en mettant en avant les concepts proposés, les limitations rencontrées et comment elles ont été surmontées.

Contexte

Radio logicielle

Le concept de radio logicielle imagine un transmetteur pour les communications mobiles comme étant un bloc de traitement de signal multifonctions et totalement reconfigurable. Il pourrait se placer juste devant un convertisseur numérique-analogique et l'antenne d'émission, afin de fournir le signal RF désiré selon le standard sélectionné (Figure 1-1). Devant la profusion de standards existants ou à venir (GSM, UMTS, Wi-Fi, Wimax, 4G, etc...), ce genre de terminal mobile universel serait une révolution.

Etat de l'art sur les architectures de transmetteurs

La tendance est de numériser progressivement la chaîne d'émission afin de se rapprocher du concept de radio logicielle. Traditionnellement, les architectures d'émission sont entièrement analogiques (Figure 1-3 et Figure 1-4). La conversion N/A est réalisée en bande de base. On distingue deux implémentations possibles selon que la transposition en RF se fait en une ou deux étapes. Ces structures sont respectivement appelées homodynes et hétérodynes. Récemment, des architectures utilisant une conversion N/A aux fréquences intermédiaires (IF) ont été proposées (Figure 1-5). Elles sont principalement basées sur des modulateurs $\Delta\Sigma$ et des mélangeurs numériques en quadrature. Enfin, ce concept est étendu aux fréquences RF (Figure 1-8). Cela permet d'utiliser des amplificateurs de puissance commutés, offrant une très bonne efficacité. A ce jour, aucune implémentation aux radiofréquences n'est reportée. Le concept est démontré dans la littérature théoriquement et par des simulations. Le but du travail présenté ici est de démontrer par un prototype la faisabilité d'une telle architecture et sa possible implémentation dans des technologies CMOS nanométriques.

Spécifications du standard UMTS

Nous nous intéressons ici à la couche physique de l'UMTS dont les spécifications sont données par l'ETSI. En émission, l'UMTS utilise une bande de 60MHz située entre 1,92 et 1,98GHz. L'UMTS utilise une technique d'accès multiples par codage (CDMA). L'information est étalée sur des canaux larges de 5MHz, d'où le nom de WCDMA (W pour Wideband). Les spécifications qui nous intéressent sont les suivantes :

- Le masque d'émission spectrale en bande (Table 1-1 et Figure 1-13).
- Les valeurs d'ACLR (Adjacent Channel Leakage Ratio) pour les canaux adjacents et alternatifs (Table 1-2). Ces valeurs sont respectivement égales à 33 et 43dB.
- Les émissions parasites qui définissent la puissance maximale à l'antenne pour certaines bandes de fréquence (Figure 1-14 et Table 1-3). Les contraintes

proviennent principalement des bandes dédiées à la réception UMTS et DCS1800 ainsi que des bandes GSM.

• La valeur d'EVM dont le maximum est de 17,5%.

Architecture du transmetteur numérique

Choix de l'architecture

Le but de cette architecture est de fournir un signal 1 bit suréchantillonné contenant l'information du signal RF à un amplificateur de puissance commuté. L'architecture envisagée est constituée autour d'un modulateur $\Delta\Sigma$ et d'un transposeur numérique en quadrature. Le modulateur $\Delta\Sigma$ quantifie le signal numérique en une séquence à cadence rapide sur 1 bit. Le bruit de quantification apporté est repoussé en dehors de la bande utile. La transposition numérique permet de placer le signal autour de la fréquence RF porteuse voulue.

Deux architectures sont envisageables (Figure 2-5). La première utilise un modulateur $\Delta\Sigma$ passe-bande suivant une transposition numérique du signal. La seconde utilise deux modulateurs passe-bas sur les voies I et Q, suivis d'une transposition numérique sur un seul bit. La seconde solution a été retenue car elle permet de simplifier fortement le bloc de transposition RF et de réduire par deux la cadence d'échantillonnage des modulateurs $\Delta\Sigma$.

La cadence d'échantillonnage F_s du bloc de transposition est égal à 4 fois la fréquence centrale du standard (1,95GHz × 4 = 7,8Géch/s). Celle des modulateurs $\Delta\Sigma$ est alors de la moitié (3,9Géch/s). Pour rentrer dans les spécifications dynamiques du standard, les modulateurs conçus sont du troisième ordre avec un rapport de suréchantillonnage de 40 (bande passante de 100MHz).

Transposition numérique RF 1 bit

En choisissant une configuration passe-bas pour les modulateurs $\Delta\Sigma$, on a largement simplifié l'opération de transposition RF, puisqu'on ne travaille plus que sur un seul bit. Les données de sortie des modulateurs $\Delta\Sigma$ des voies I et Q sont multipliées numériquement par un sinus et un cosinus à la fréquence centrale, échantillonnés à F_s . Cette multiplication numérique revient à faire une opération de multiplexage entre les voies I et Q, telle que la sortie est la séquence constituée par $[I,Q,\overline{I},\overline{Q}]$. Cette opération devient très simple à réaliser sur un faible nombre de bits. Par contre, un problème de synchronisation des deux voies apparaît. En effet, les modulateurs fonctionnent de manière synchrone et les voies I et Q ne sont plus en quadrature lors du multiplexage. Une image du canal apparaît alors de l'autre côté de la porteuse (Figure 2-7). Pour éviter ce phénomène, une interpolation linéaire est constamment réalisée sur la voie Q avant les modulateurs $\Delta\Sigma$.

Architecture proposée

L'architecture proposée est présentée sur la Figure 2-16. Elle est basée sur les deux modulateurs $\Delta\Sigma$ et le bloc de transposition RF décrit plus haut. D'autres blocs sont nécessaires dans cette chaîne de transmission. Ces blocs sont les suivants :

- Un traitement en bande de base qui met en forme les signaux d'entrée selon le standard considéré.
- Un bloc de conversion de cadence qui réalise une conversion non entière et suréchantillonne les signaux jusqu'à $F_s/2$.
- Les deux modulateurs ΔΣ passe-bas qui transforment le signal numérique d'entrée en un signal 1 bit, dont le bruit de quantification est repoussé hors bande.
- Un bloc de transposition numérique RF sur 1 bit.
- Un amplificateur de puissance commuté.
- Un filtre d'antenne

Le choix a été fait de considérer non pas un canal UMTS, mais la totalité de la bande du standard (soit 60MHz), afin d'avoir un bruit relativement uniforme dans la bande passante.

Le traitement en bande de base

Le traitement en bande de base est constitué de blocs permettant la mise en forme du signal (Figure 2-17). A partir des données à transmettre, le signal est étalé sur 3,84MHz et embrouillé afin d'avoir son propre code. Ensuite, un filtre à cosinus surélevé avec un roll-off de 0,22 permet de limiter la bande occupée par le canal à 5MHz. Des filtres demi-bandes permettent de suréchantillonner le signal afin d'atteindre une cadence de 122,88Méch/s. Finalement, un algorithme numérique de CORDIC est utilisé pour placer le canal de 5MHz sur une sous-porteuse dans la bande de 60MHz du standard. Le signal de sortie généré est présenté sur la Fig 2-10.

La conversion de cadence

La cadence du signal en bande de base est dépendante de la cadence symbole (3,84Méch/s). C'est un multiple de cette cadence (122,88Méch/s, ici). Par contre, la cadence à l'entrée des modulateurs $\Delta\Sigma$ est de 3,9Géch/s. Pour palier au fait que le rapport entre ces deux fréquences soit non entier, on peut rajouter un décalage sur la fréquence de sous-porteuse, en bande de base, selon la Table 2-2.

Ensuite, le signal doit être suréchantillonné par 32 (Figure 2-20). Des simulations ont montré qu'un premier filtre FIR demi-bande très efficace permet de s'affranchir du filtrage des étages suivants. Ces étages deviennent de simples interpolateurs d'ordre 1, relativement faciles à implémenter. En effet, les images résultantes de ce manque de filtrage seront noyées dans le bruit de quantification hors-bande généré par les modulateurs $\Delta\Sigma$.

Les modulateurs $\Delta \Sigma$ numériques

Un modulateur $\Delta\Sigma$ est composé d'un quantificateur, assimilable à une source de bruit blanc, et d'une boucle de contre-réaction. Ce système possède des fonctions de transfert différentes pour le signal et pour le bruit de quantification. Pour le signal, la fonction de transfert est plate dans la bande passante, tandis que pour le bruit, elle présente une fonction de filtrage qui atténue le bruit en bande et le repousse en dehors de la bande utile. On peut ainsi coder, sur très peu de bits mais avec une très bonne dynamique, des signaux limités en bande.

L'architecture des modulateurs passe-bas du troisième ordre est présentée sur la Figure 2-23. Elle a la particularité d'avoir une boucle de retour permettant de placer des zéros aux extrémités de la bande considérée, permettant ainsi d'élargir la bande passante et d'avoir un bruit de quantification relativement plat dans celle-ci (Figure 2-24).

Les performance simulées indiquent un ACPR d'environ 75dB pour un canal de 5MHz et un SNDR de 76dB (13 bits efficaces).

L'amplificateur de puissance et les filtres d'antenne

L'amplificateur de puissance est ici considéré comme un convertisseur N/A. Sa topologie est relativement simple, puisqu'elle consiste en une chaîne d'inverseurs de dimensions croissantes (Figure 2-11). L'efficacité théorique d'un tel étage est de 100%, mais

des pertes lors des commutations et de la puissance dissipée statiquement ou dynamiquement réduisent cette efficacité.

D'autres non-idéalités perturbent le signal de sortie. L'asymétrie des fronts est compensée par une structure de sortie différentielle. Par contre, le jitter sur le signal de sortie dégrade le spectre en augmentant le bruit dans la bande.

Le filtre d'antenne doit être capable d'atténuer le bruit hors bande, notamment dans les bandes de réception d'autres standards. Des technologies telles que les filtres BAW pourraient permettre un filtrage efficace de ce genre de signal.

Conception système du modulateur $\Delta\Sigma$

A partir de la structure du modulateur $\Delta\Sigma$ définie précédemment, des optimisations sont nécessaires pour permettre de réaliser les opérations logiques à haute cadence (3,9Géchs/s) à l'intérieur du système. Dans un premier temps, l'accumulateur présent dans l'architecture précédente sera remplacé par un intégrateur (Figure 3-2). Ensuite, les coefficients du modulateur vont être arrondis à la puissance de deux la plus proche, selon la Table 3-1, afin que ces opérations ne prennent aucun temps de calcul. En effet, elles consisteront en de simples décalages des bits des signaux internes. Les performances dynamiques sont peu affectées. Le SNDR est dégradé d'environ 3dB tandis que l'ACLR est de 74,7dB et 72,2dB, respectivement pour les canaux adjacents et alternatifs.

Utilisation de l'arithmétique redondante

Le chemin critique est constitué par un additionneur à 4 entrées précédant le 2^{ème} registre (Figure 3-4 et Figure 3-5). En utilisant une architecture classique en complément à 2, le chemin critique est réduit à deux additions successives sur environ 16 bits. La cadence d'échantillonnage visée est de 3,9Géch/s, soit environ 250ps de période. Ce qui laisse moins de 125ps pour une addition 16bits (en omettant le temps de propagation des bascules, qui sera bien sûr non négligeable).

En utilisant des additionneurs à retenue bondissante (RCA (Figure 3-7)), le temps de propagation est environ égal au nombre de bits multiplié par le temps de propagation unitaire d'un additionneur complet (FA), ce qui est bien supérieur au temps disponible. Des structures à anticipation de retenue permettent d'améliorer le temps de calcul total. Malheureusement,

même avec des portes logiques rapides (en logique DPL, par exemple (Figure 3-9)), la contrainte de temps ne peut être respectée.

L'utilisation d'une arithmétique redondante, pour remplacer l'arithmétique en complément à 2 permettrait d'atteindre la cadence désirée. En arithmétique redondante de type Borrow-Save (BS), chaque signal sur N bits est codé par 2 x N bits, la moitié codant pour du positif et l'autre moitié pour du négatif (Figure 3-10). Ainsi, un nombre donné peut être codé de plusieurs façons différentes, d'où le nom de « redondant ». Ce codage permet de réaliser des additions en temps constant, sans propagation de retenue, ce qui nous avantage dans le type d'architecture implémentée.

On construit, à partir de cellules FA traditionnelles, des cellules appelées signed-FA, qui constitueront les blocs de base de l'architecture (Figure 3-12). Chaque bloc est détaillé dans les figures suivantes (Figure 3-17 à Figure 3-21). Le chemin critique est maintenant composé d'au maximum trois cellules FA successives. Les performances du modulateur sont quasiment identiques aux performances précédentes.

Quantification non exacte et pré-évaluation du signal de sortie

Le quantificateur de sortie est sur deux niveaux (1 bit) et définit donc le signe du signal entrant. Malheureusement, avec un nombre codé en arithmétique redondante, on a difficilement accès à cette information. En effet, déterminer le signe d'un nombre codé en arithmétique redondante revient à propager une retenue à travers tous ses bits. On a déplacé le problème du chemin critique sur le quantificateur.

Une étude des performances du modulateur en fonction du nombre de bits pris en compte dans la quantification a permis de mettre en évidence que les paramètres dynamiques sont très peu dégradés si on réduit le nombre de bits du quantificateur (Figure 3-24). Dans notre cas, nous avons pu réduire ce nombre à 3 bits. De plus, une étude logique a montré, dans l'architecture particulière implémentée ici, que le signe pouvait être déterminé par une fonction à 3 entrées. Les performances sont très légèrement dégradés (Table 3-5). L'ACLR est de 68,8 et 67,4dB pour des offsets de 5 et 10MHz.

Même si la fonction logique du quantificateur a été réduite, elle occupe un certain temps de calcul. L'idée a été de traiter cette opération en parallèle avec le dernier étage (Figure 3-26), en pré-évaluant le signe du signal de sortie.

Conception circuit du transmetteur numérique

Description du circuit intégré

Le circuit intégré contient les blocs de suréchantillonnage par 16, les modulateurs $\Delta\Sigma$, le bloc de transposition numérique et les buffers de préamplification. A cela s'ajoutent les blocs de génération (basé sur une DLL) et de distribution des horloges, ainsi que les blocs de contrôle (Figure 4-1 et Figure 4-2).

Le premier circuit prototype a été conçu dans une technologie CMOS 90nm de STMicroelectronics. Le layout est présenté sur la Figure 4-3. Il mesure 3×1mm² et comporte 96 pads. On trouve 13 pads d'entrée numériques pour les voies I et Q sur les parties hautes et basses du pad ring, ainsi que des sorties numériques parallélisées. A gauche se trouve l'entrée d'horloge et à droite les pads de sortie RF. Un second prototype a ensuite été conçu dans la même technologie afin de corriger les erreurs et d'améliorer le fonctionnement du circuit. Les modifications apportées sont détaillées dans le chapitre suivant.

Le bloc de conversion de cadence

Le bloc de conversion de cadence a pour rôle de suréchantillonner le signal entrant de 243,75Méch/s jusque 3,9Géch/s. Ce suréchantillonnage est du premier ordre et est donc facilement construit avec des bascules cadencées avec des horloges à ces fréquences. Deux schémas d'horloges ont été utilisés pour chacun des prototypes (Figure 4-4 et Figure 4-5). Dans le premier prototype, le circuit intégré génère l'horloge à 250MHz à partir de celle à 4GHz et les instruments sont contrôlés avec cette horloge. Dans le deuxième prototype, c'est l'inverse qui est utilisé. L'horloge à 250MHz est amenée de l'extérieure et resynchronisée en interne. Sur la voie Q, le circuit permettant l'interpolation linéaire, pour éviter la mauvaise synchronisation des 2 voies, est présenté sur la Figure 4-7.

Les bascules utilisées dans ce bloc sont des bascules dynamiques utilisant un seul front d'horloge (TSPCFF). Ces bascules ont été créées pour pouvoir fonctionner à haute cadence grâce à un système de précharge et d'évaluation. Son schéma et son layout sont présentés sur la Figure 4-8. Son mécanisme est expliqué sur la Figure 4-9.

La conception du circuit du modulateur $\Delta\Sigma$ numérique

Dans le chapitre précédent, on a montré qu'avec l'arithmétique redondante, 3 cellules FA au maximum doivent être traitées pendant une période d'horloge. L'idée a donc été de diviser chaque période en trois parties, ou couches. Pour la conception circuit des modulateurs, la logique dynamique a été identifiée comme la plus rapide et la seule pouvant, en CMOS 90nm, permettre au système de rentrer dans la période désirée. L'utilisation de ce type de logique évite de recourir à des bascules. Par contre, on a besoin d'une horloge pour chaque bloc. Nous avons donc besoin de trois horloges (une pour chaque couche), chacune déphasée d'un tiers de période par rapport à l'autre. Une DLL, détaillée plus loin, permettra de générer ces horloges. L'arrangement des cellules est présenté sur la Figure 4-12.

Les cellules FA en logique dynamique sont totalement différentielles et sont basées sur deux étages (Figure 4-13). Un premier qui aura les fonctions de précharge et d'évaluation, selon la polarité de l'horloge. Le deuxième sera un inverseur trois-états, le troisième état étant une fonction de maintien de l'information en sortie. Chaque cellule fonctionne donc en moins de 83ps (tiers de période).

Ces cellules sont très sensibles à la non-différentialité des entrées, du fait que le système soit rebouclé. Ainsi, un circuit d'initialisation a dû être intégré au circuit des cellules de base, afin de pouvoir démarrer correctement. Sur le premier prototype, les sorties ont été placées dans un état différentiel en tirant les potentiels à travers un transistor vers leurs valeurs respectives (Figure 4-15). Cette technique ne fonctionne que sur une gamme de fréquences donnée, puisque la commande d'initialisation doit arriver à un moment opportun par rapport aux horloges. Sur le second prototype, un circuit, comprenant des transistors couplés, a été développé afin de garantir la différentialité des signaux et un fonctionnement à toutes les fréquences (Figure 4-16). Le layout du cœur numérique du circuit est présentée sur les Figure 4-17 et Figure 4-18.

Génération et distribution des horloges

Une DLL est utilisée pour générer 3 horloges déphasées à partir d'une horloge principale (Figure 4-19). Elle consiste en des éléments de retard contrôlables et d'un détecteur de phase qui fournit une information sur le déphasage de l'horloge de sortie (360°) par rapport à celle d'entrée. Cette information est traitée par une pompe de charge qui contrôle la valeur des retards.

La ligne à retards est composée d'inverseurs enchaînés, qui comprennent deux transistors supplémentaires (un NMOS et un PMOS) dans leur chemin de charge et de décharge (Figure 4-20). Ainsi, en fonction de la tension appliquée sur ces transistors, l'inverseur sera plus ou moins rapide. Le détecteur de phase est basé sur une bascule RS. La

pompe de charge utilise une capacité sur laquelle elle vient ajouter ou prélever une certaine quantité de charge, définie par le courant utilisé ($100\mu A$, ici) dans la pompe de charge. On obtient en simulation de très bonnes caractéristiques (Table 4-1).

Mélangeur numérique et étage de sortie

La structure du mélangeur numérique est basée sur des portes de transmission pipelinées, afin de réaliser l'opération de multiplexage (Figure 4-26). Une attention particulière a été portée sur le fait que les chemins de données ne devaient pas dépendre des données traitées. Pour cela une bascule a été insérée dans l'architecture (Figure 4-27). L'étage de sortie est composé d'une ligne de buffers croissants. Un diagramme de l'œil de la sortie RF, obtenu en simulation, est présenté sur la Figure 4-28.

Résultats expérimentaux

Premier circuit prototype

Le matériel de test pour le premier circuit est décrit, afin de pouvoir d'une part, analyser le spectre de la sortie analogique et d'autre part, acquérir les données numériques de sortie (Figure 5-1 et Figure 5-2). Les signaux sont générés sur un générateur arbitraire (AWG 420). Des cartes basées sur des FPGA ont été fabriquées pour suréchantillonner ces signaux jusqu'à 250Méch/s.

Le circuit intégré a été bondé sur un substrat de $24 \times 12 \text{mm}^2$ sur des pistes de cuivre large de 50µm et espacées de 50µm (Figure 5-3). Ce substrat est ensuite soudé sur une carte fille abritant tous les composants utiles à l'alimentation et aux contrôles. Deux connecteurs la relient à une carte mère abritant les FPGA (Figure 5-4).

Les mesures sur ce premier prototype n'ont pas été fructueuses. Le circuit n'est pas fonctionnel à haute cadence car de larges variations sont présentes sur les alimentations, dues aux pics de courant à travers les bondings (Figure 5-5 et Figure 5-6). Malheureusement, à cause du système d'initialisation, le système n'est pas fonctionnel à plus basse fréquence. Le fonctionnement du cœur n'a donc pas pu être testé. Par contre, nous avons pu tirer des informations sur les aspects du circuit à retravailler et quelques mesures sur l'étage de sortie, notamment au niveau de sa consommation (Figure 5-7 et Figure 5-8).

Deuxième circuit prototype : changements et protocoles de tests

Les principaux changements apportés sont les suivants :

- L'alimentation a été retravaillée (regroupement de toutes les alimentations, placement judicieux des pads d'alimentation et de masse) et les pads ont été espacés afin de faciliter l'étape d'assemblage.
- Des capacités de découplage ont été ajoutées sur le circuit intégré.
- Le système d'initialisation a été revu (décrit dans une partie précédente).

Les protocoles de test sont sensiblement identiques à ceux du premier circuit, à la différence près que les sorties numériques ont été supprimées (Figure 5-11).

Deuxième circuit : résultats de mesure pour une horloge à 2.6GHz

Le circuit fonctionne comme désiré jusqu'à une fréquence d'horloge de 4GHz (au lieu des 7,8GHz prévus). Ainsi, le circuit peut adresser une bande passante de 50MHz jusqu'à une fréquence porteuse de 1GHz (voire 3GHz si la bande image est considérée ; on observe dans ce cas une atténuation due au sinus cardinal). Le signal de sortie RF a été acquis avec un oscilloscope numérique et le signal, une fois traité comme un signal numérique, a révélé la fonction de transfert attendue pour les modulateurs $\Delta\Sigma$ (Figure 5-13).

Avec une fréquence d'horloge à 2,6GHz, une bande autour de 650MHz a pu être adressée (1,95GHz pour la bande image). Le signal d'entrée est soit un canal WCDMA de 5MHz de large modulé en QPSK, soit une sinusoïde placée aux alentours de 5MHz. L'ACPR, le SNDR et l'EVM ont été étudiés en fonction de la puissance du canal ou de la sinusoïde. Dans le tableau suivant sont regroupées les caractéristiques mesurées, dont toutes les figures sont données (Figure 5-14 à Figure 5-23). Le circuit mesuré rentre dans les spécifications pour le standard UMTS.

		Horloge à 2,6GHz		
		Canal à 650MHz	Canal à 1,95GHz (image)	
ACPR (canal de 5MHz de large)		53,6dB	44,3dB	
Puissance max du canal		-3,9dBm	-15,8dBm	
EVM		1,24%	3,42%	
Jitter de sortie		13,2ps _{RMS}		
SNDR (BW = 30MHz)		53,6dB	40,3dB	
Bruit en bande		-129,5dBm/Hz	-129,4dBm/Hz	
Puissance de sortie en pic		3,1dBm	-8,59dBm	
Consommation	total	69mW (1V)		
	Etage de sortie	39mW		
	Coeur	$2 \times 15 \mathrm{mW}$		

Deuxième circuit : résultats de mesure en fonction de la fréquence

La consommation du circuit augmente en fonction de la fréquence avec une pente d'environ 20mW/GHz (Figure 5-24). L'ACPR, ainsi que le SNDR, mesurés à différentes fréquences restent relativement identiques aux valeurs mesurées précédemment (Figure 5-25à Figure 5-27). L'EVM reste toujours inférieur à 6% (Figure 5-28). Par contre, la puissance du canal varie fortement avec la fréquence. La variation va jusqu'à 4dB (Figure 5-29). L'explication n'est pas encore claire mais cela provient probablement du balun utilisée pour la conversion différentielle vers single-ended. Le jitter de sortie augmente avec la fréquence, comme attendu à cause des perturbations des éléments logiques sur les alimentations et les chemins d'horloge. Pour la plupart des fréquences, le système rentre dans les spécifications du standard UMTS, qui est un des plus contraignants.

Une comparaison est effectuée entre ce travail et un travail réalisé sur une architecture identique mais fonctionnant en fréquences intermédiaires (Table 5-2). Cette comparaison montre une nette avancée de nos travaux, surtout en termes de fréquence de fonctionnement.

Conclusion

Pour des applications de communications mobiles, un transmetteur numérique RF utilisant la modulation $\Delta\Sigma$ a été proposé et démontré. Un prototype en technologie 90nm CMOS a été développé, qui respecte les spécifications de la plupart des standards, tels que

l'UMTS. Un des avantages potentiels d'un signal RF numérique codé sur 1 bit est la possibilité d'utiliser un amplificateur de puissance commuté, ayant une grande efficacité. L'architecture démontrée ici est la première chaîne d'émission utilisant une modulation $\Delta\Sigma$ sur 1 bit reportée dans la littérature pour des fréquences RF.

Les directions futures concernent principalement la reconfigurabilité dynamique du système pour différents standards (DCS1800, etc...) et l'implémentation de cette architecture dans des technologies plus poussées (65nm, par exemple). En effet, les techniques développées ici pourront être implémentés avec une conception circuit plus simple. Par exemple, la logique dynamique, contraignante en termes de gestion des horloges, pourra être avantageusement remplacée par de la logique statique rapide comme la DPL, grâce à un process technologique plus rapide.

Dans un futur proche, le filtrage devra aussi être étudié. Des filtres BAW pouvant répondre à la demande de filtrage sont actuellement étudiés dans le projet européen MOBILIS. D'autres techniques pouvant réduire les contraintes de filtrage sont aussi à l'étude, comme par exemple, un filtrage numérique sur le signal de sortie (thèse d'Axel Flament).

Les transmetteurs numériques à base de modulateurs $\Delta\Sigma$ sont de bons candidats pour remplacer avantageusement les architectures analogiques actuelles des transmetteurs mobiles. Ils peuvent offrir de la reconfigurabilité, de la flexibilité, de la robustesse, une consommation réduite, une meilleure efficacité et une meilleure intégration. Mais beaucoup de verrous technologiques doivent encore être surmontés...